

FIG. 3A

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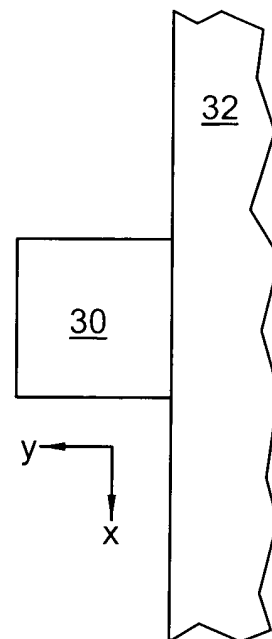
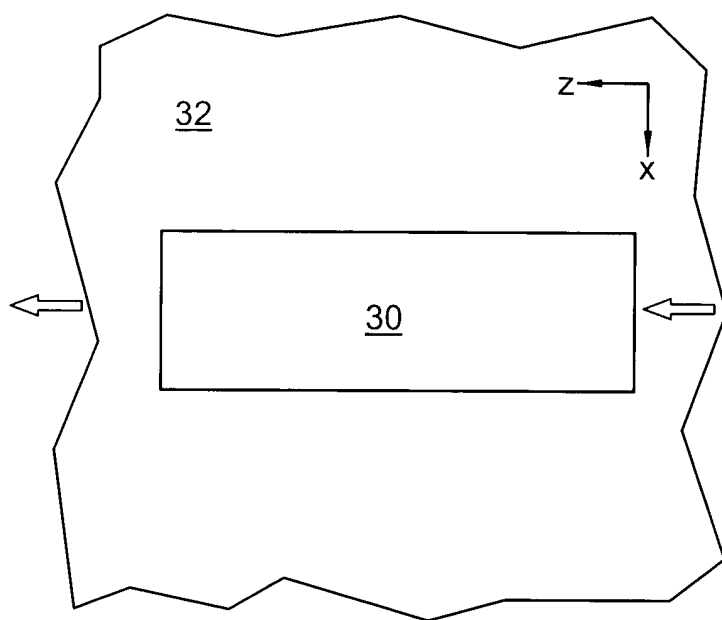


FIG. 3B

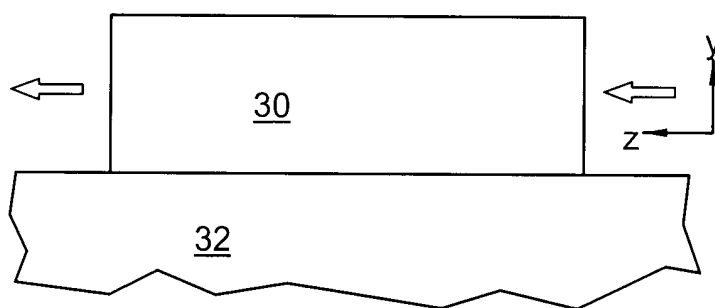


FIG. 3C

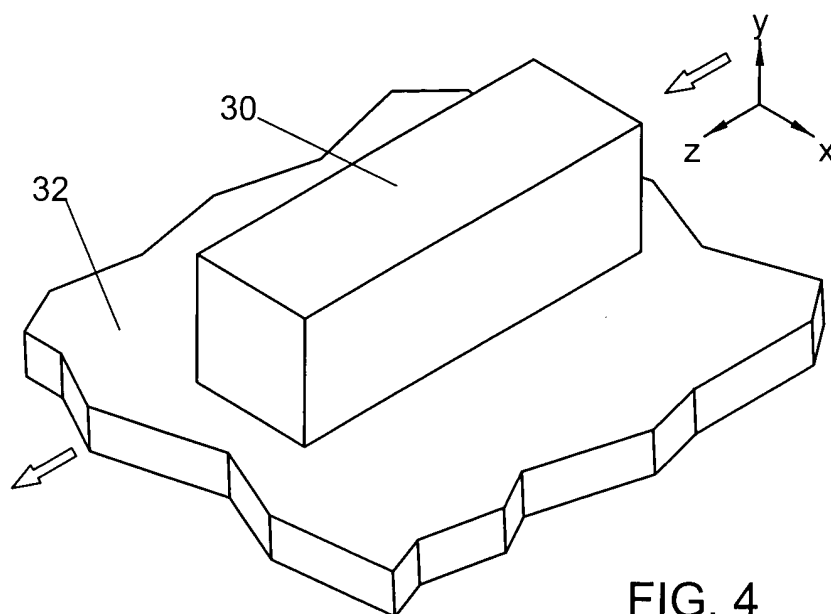


FIG. 4

FIG. 5A

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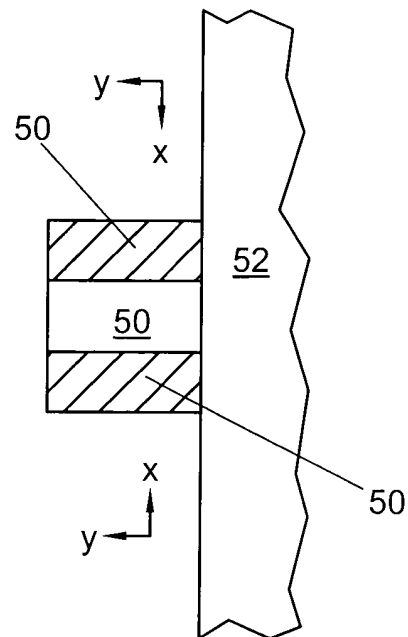
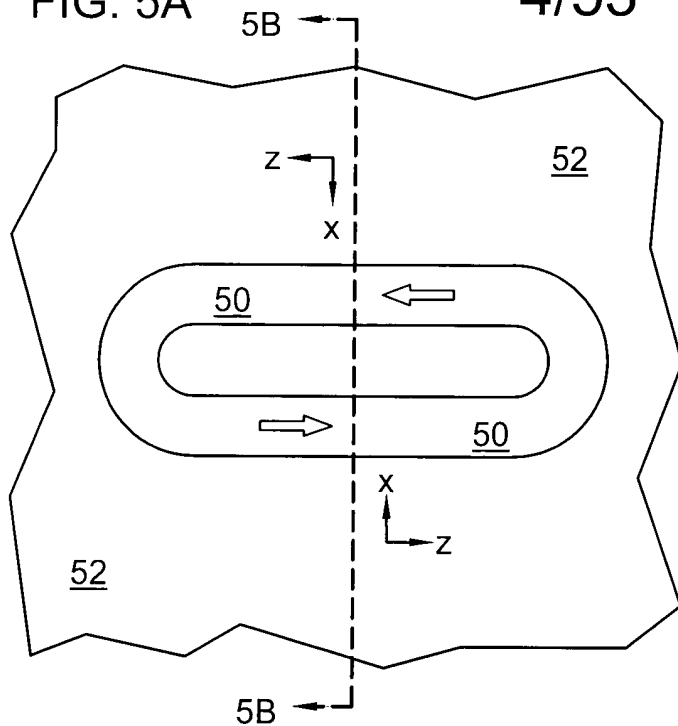


FIG. 5B

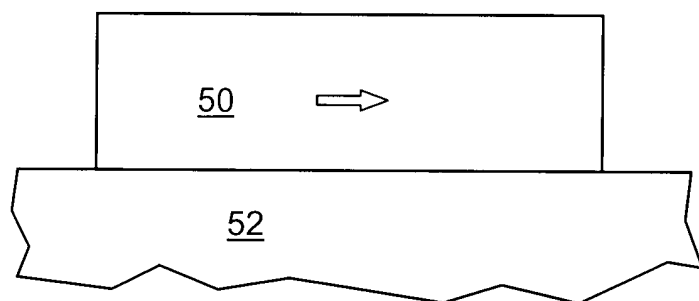


FIG. 5C

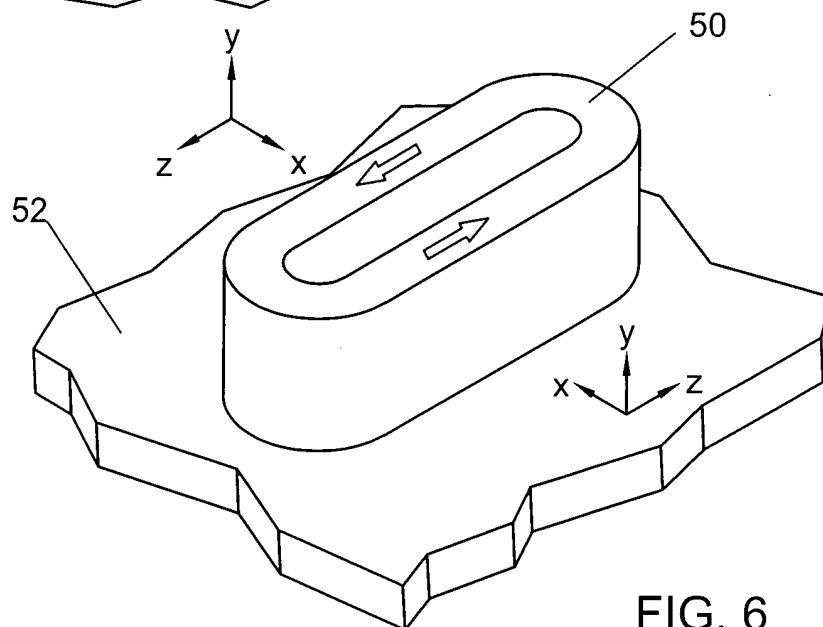


FIG. 6

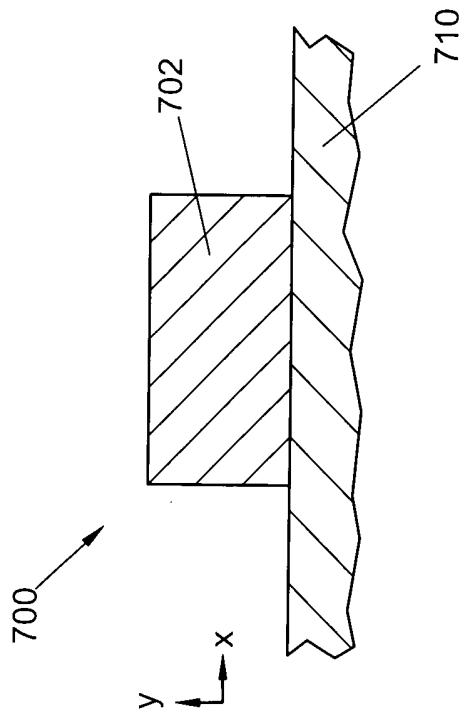


FIG. 7

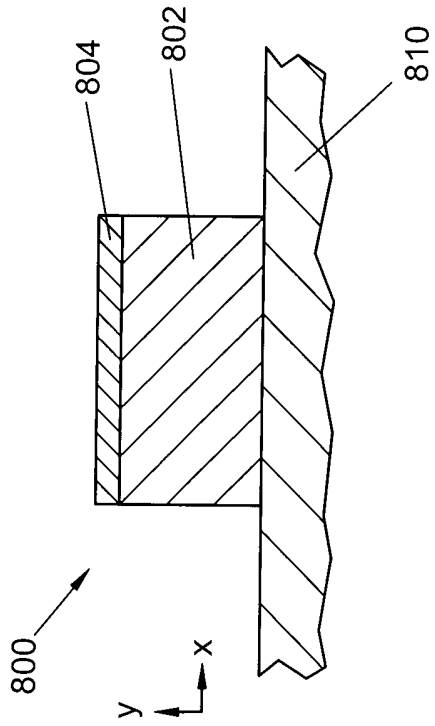


FIG. 8

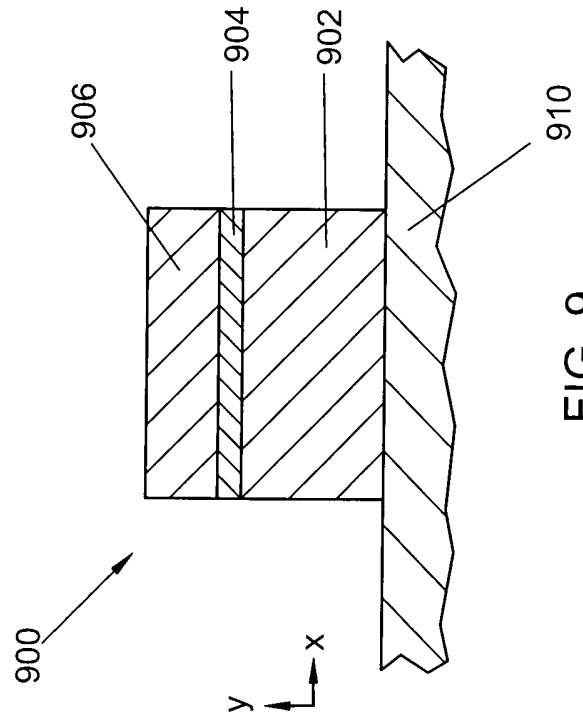


FIG. 9

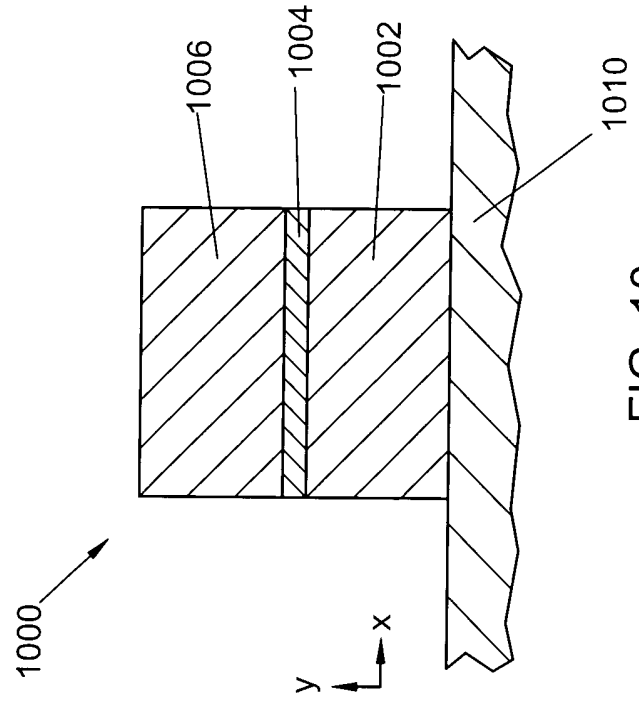


FIG. 10

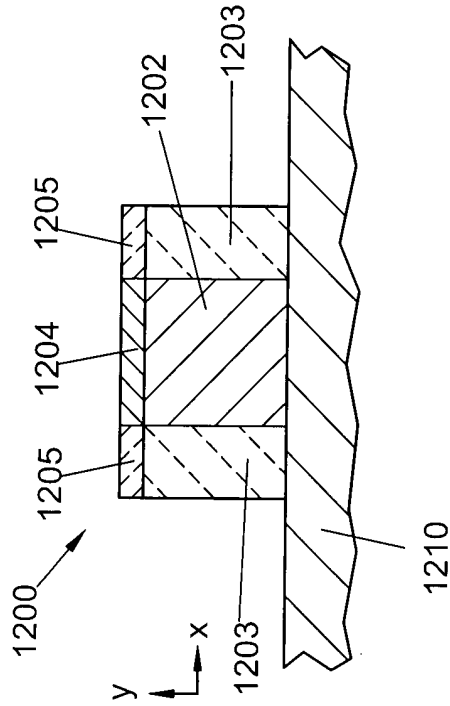


FIG. 11

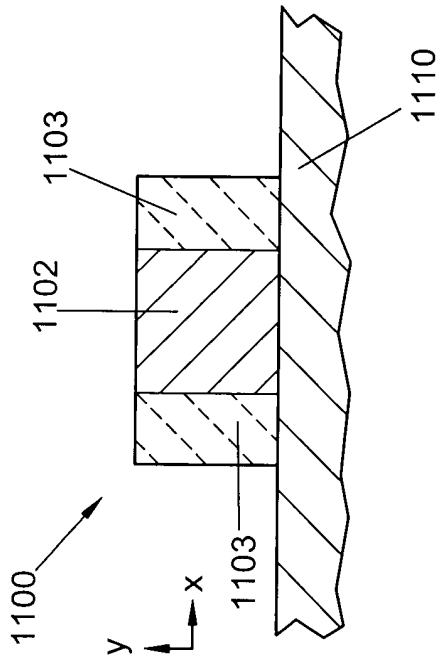


FIG. 12

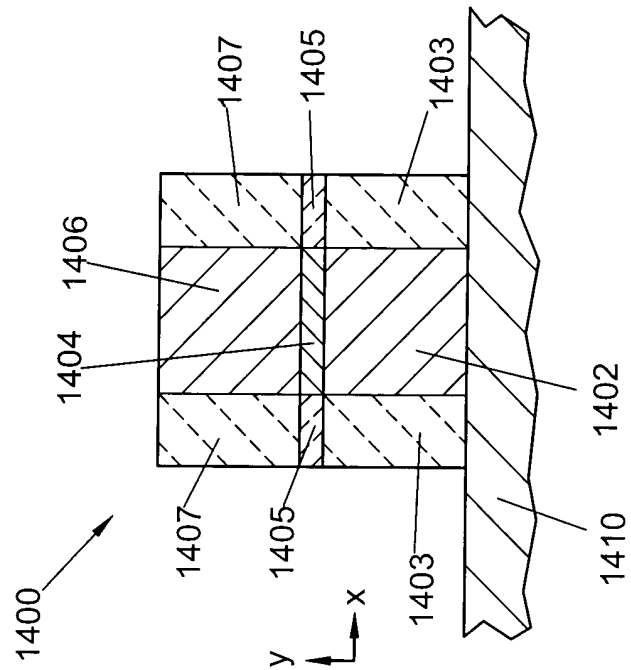


FIG. 13

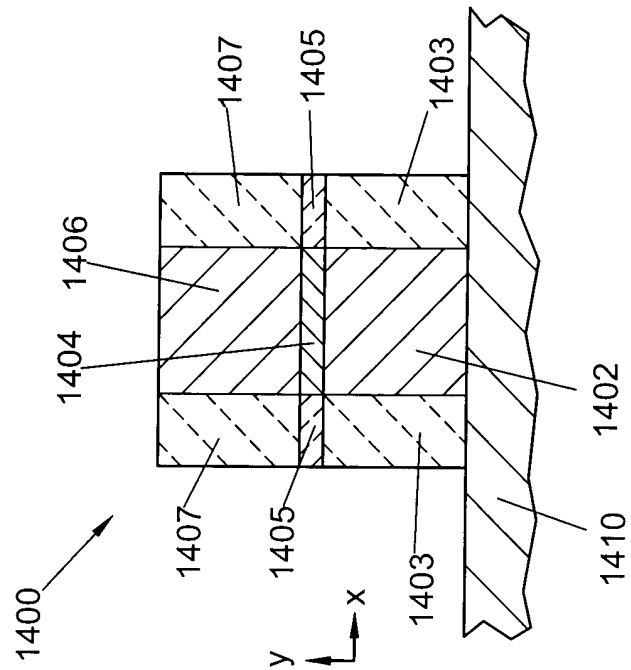


FIG. 14

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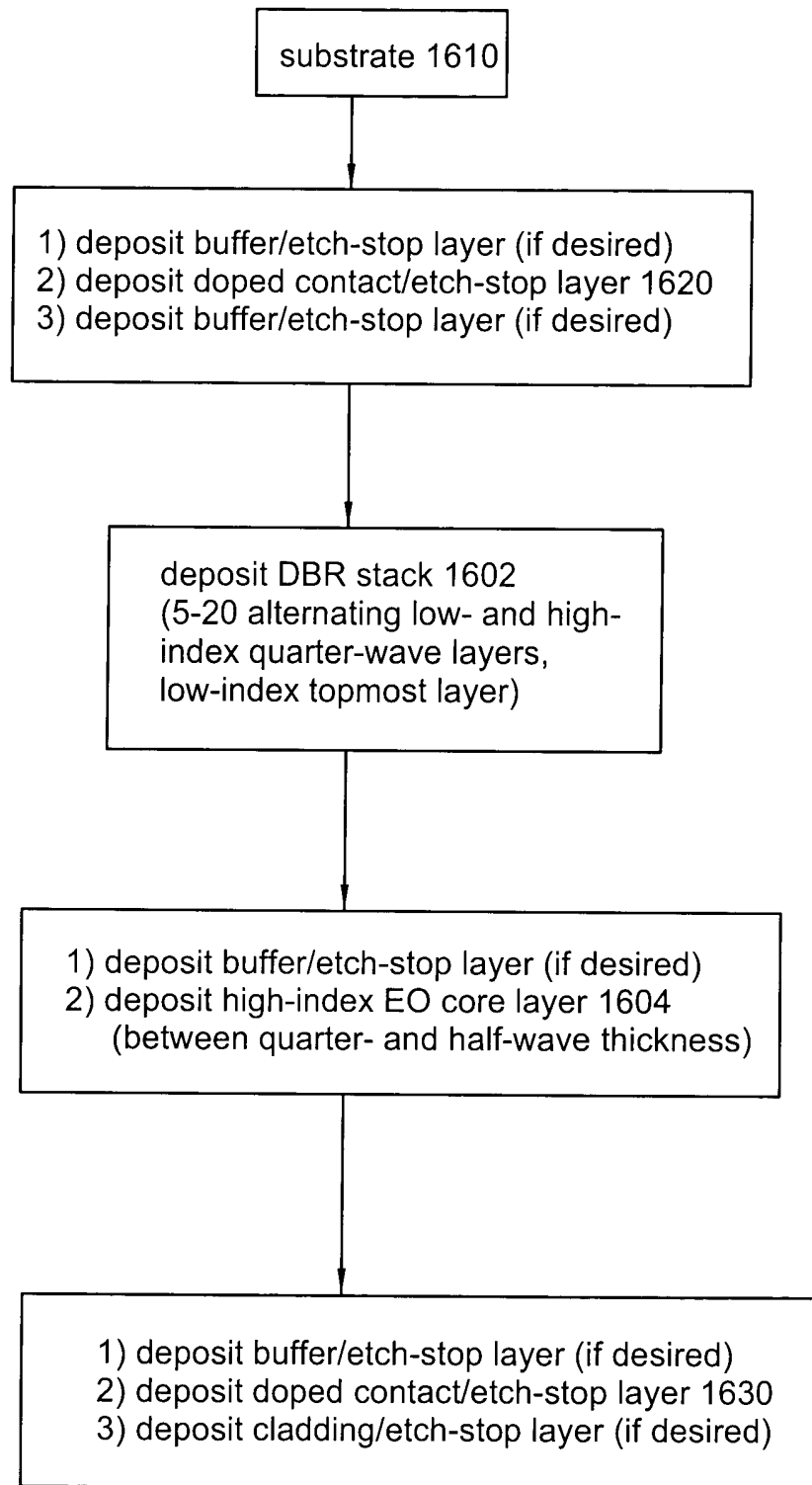


FIG. 15

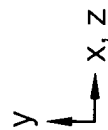


FIG. 16



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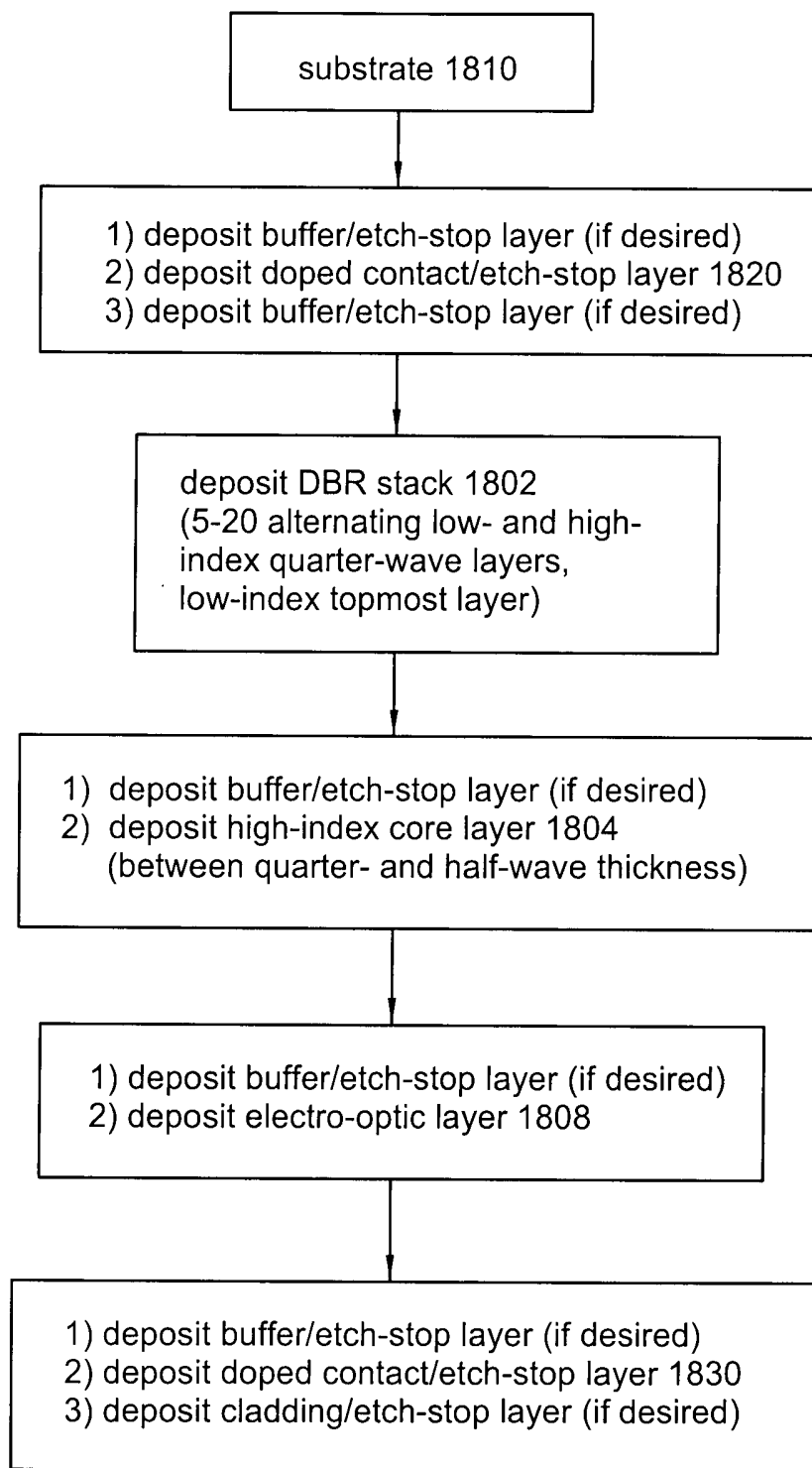


FIG. 17

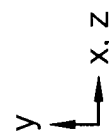


FIG. 18

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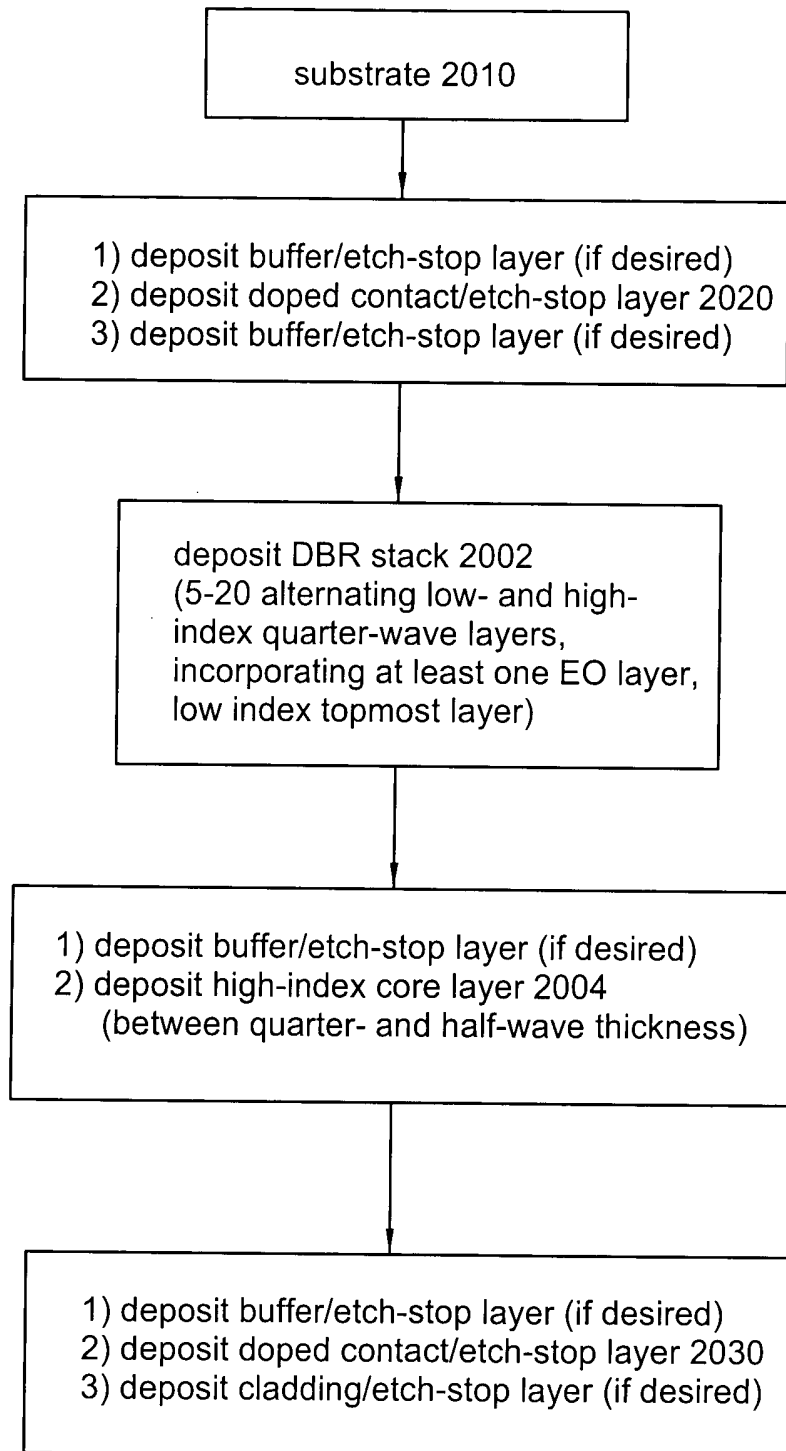


FIG. 19

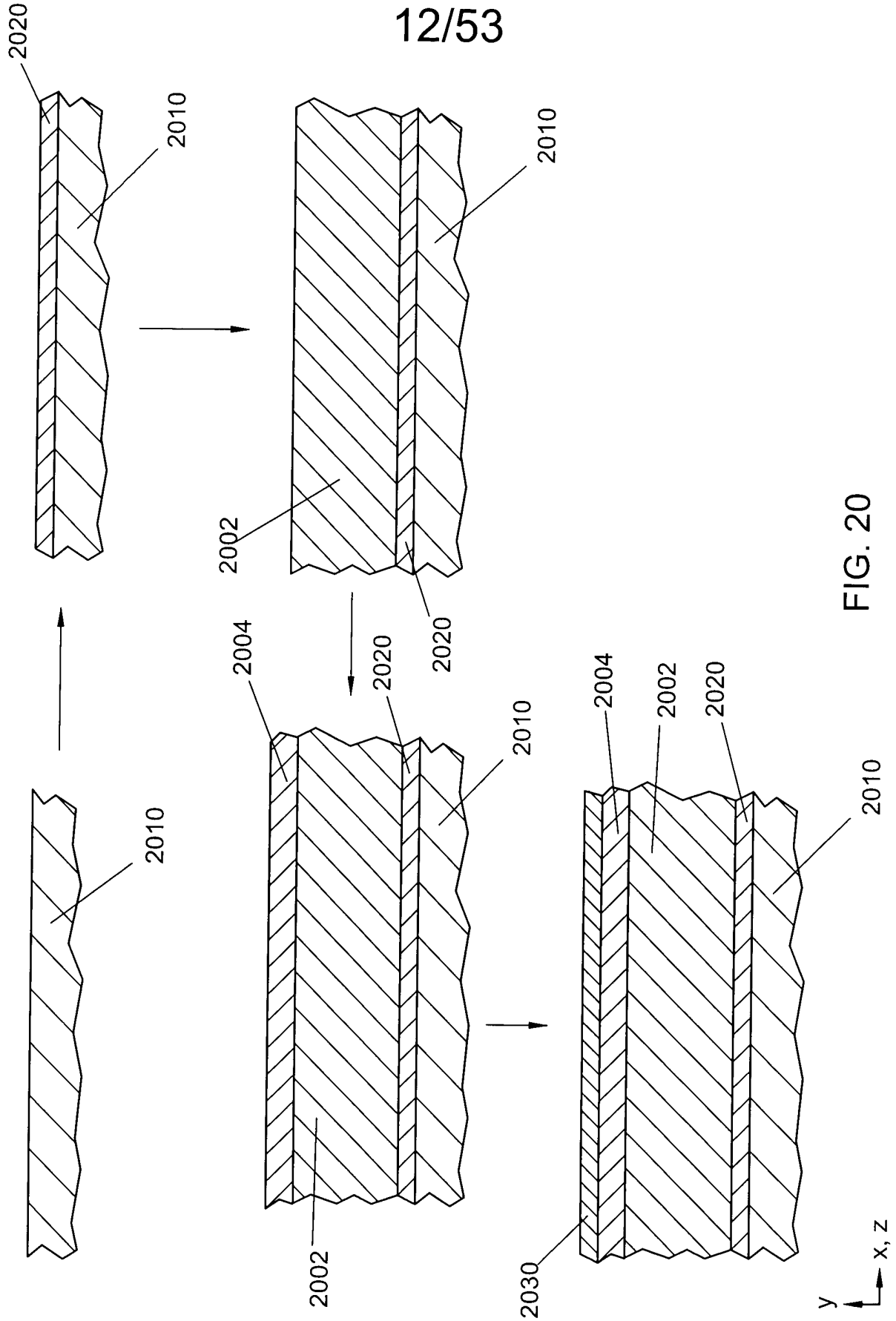


FIG. 20

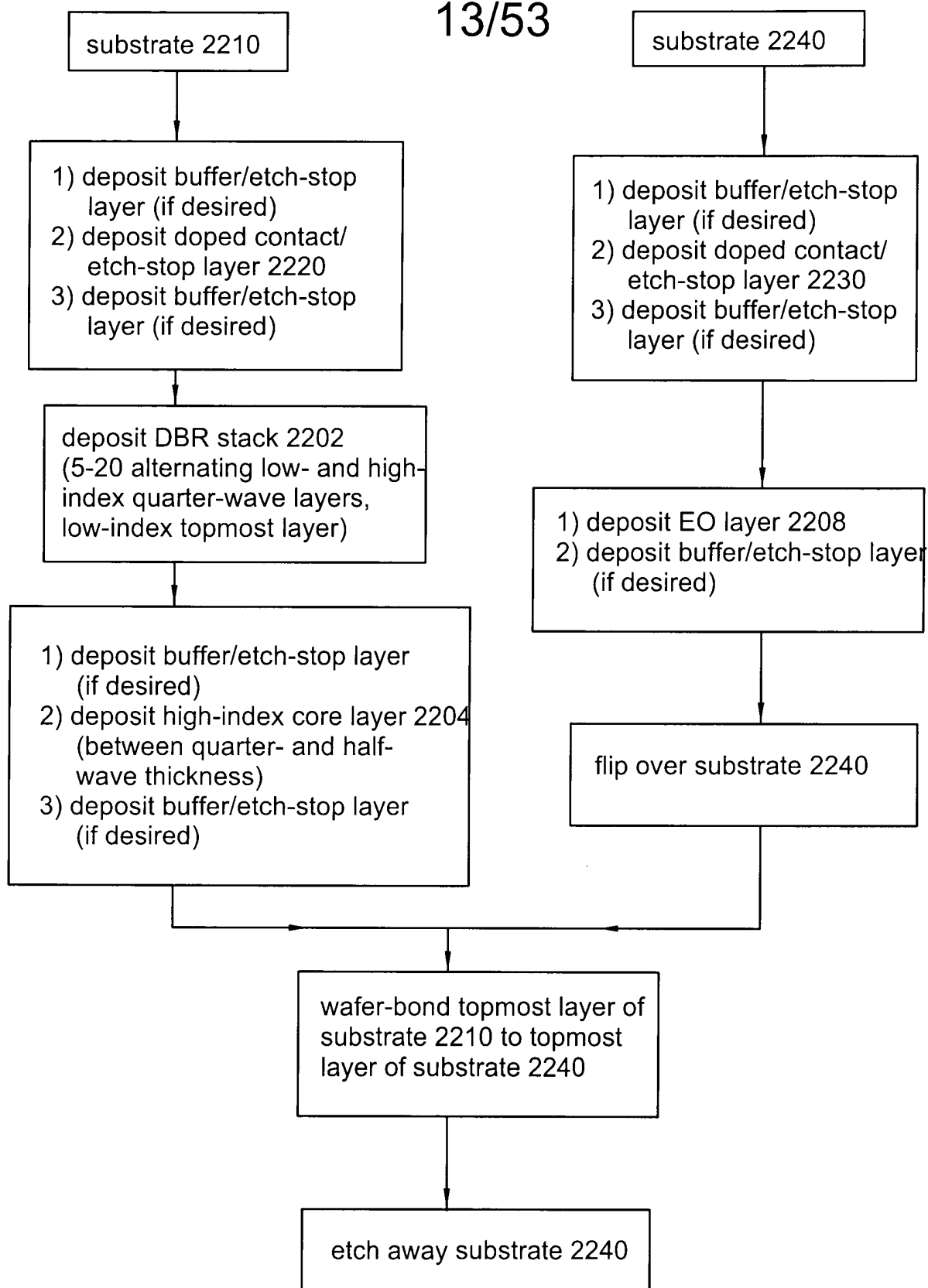


FIG. 21

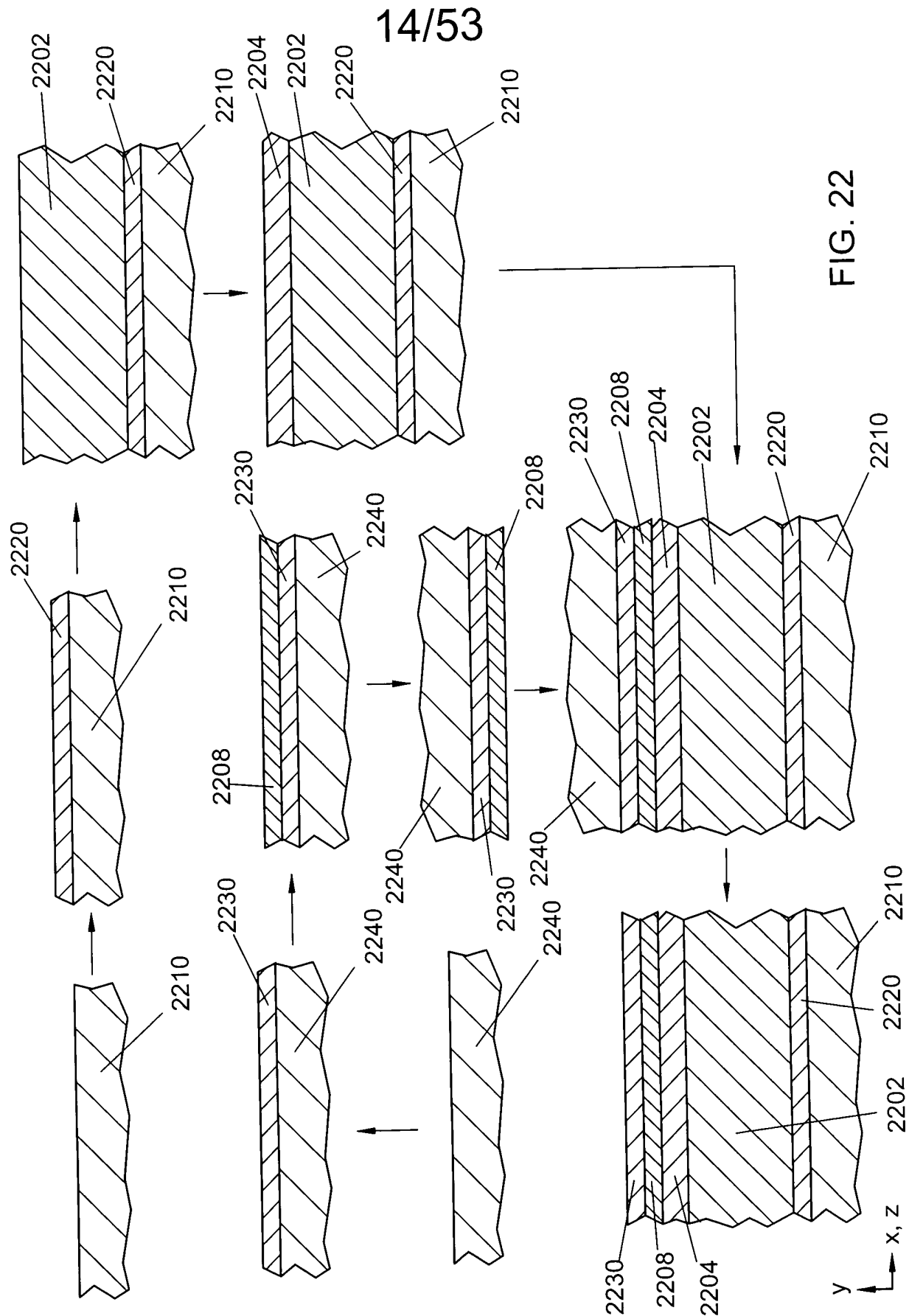


FIG. 22

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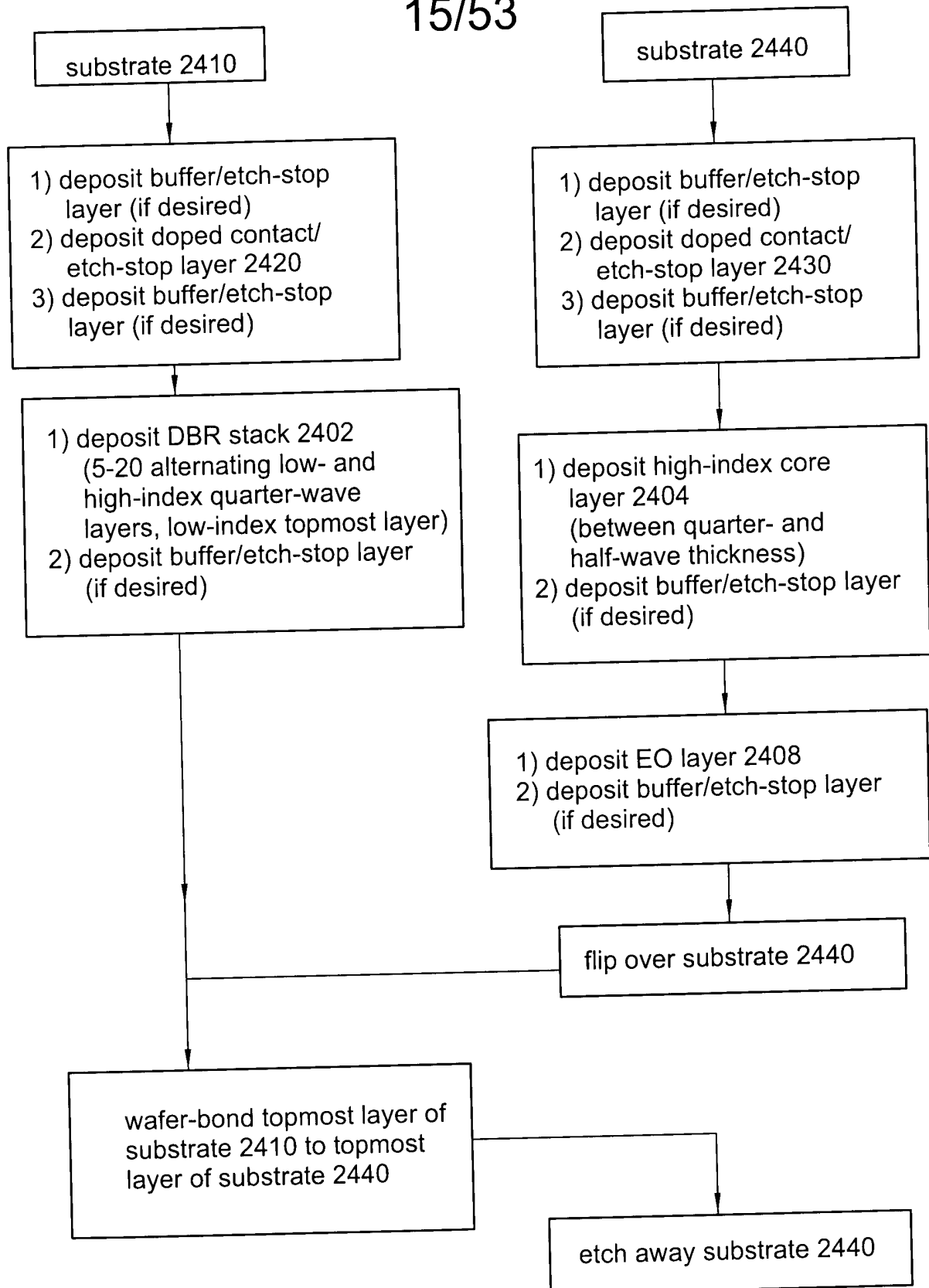


FIG. 23

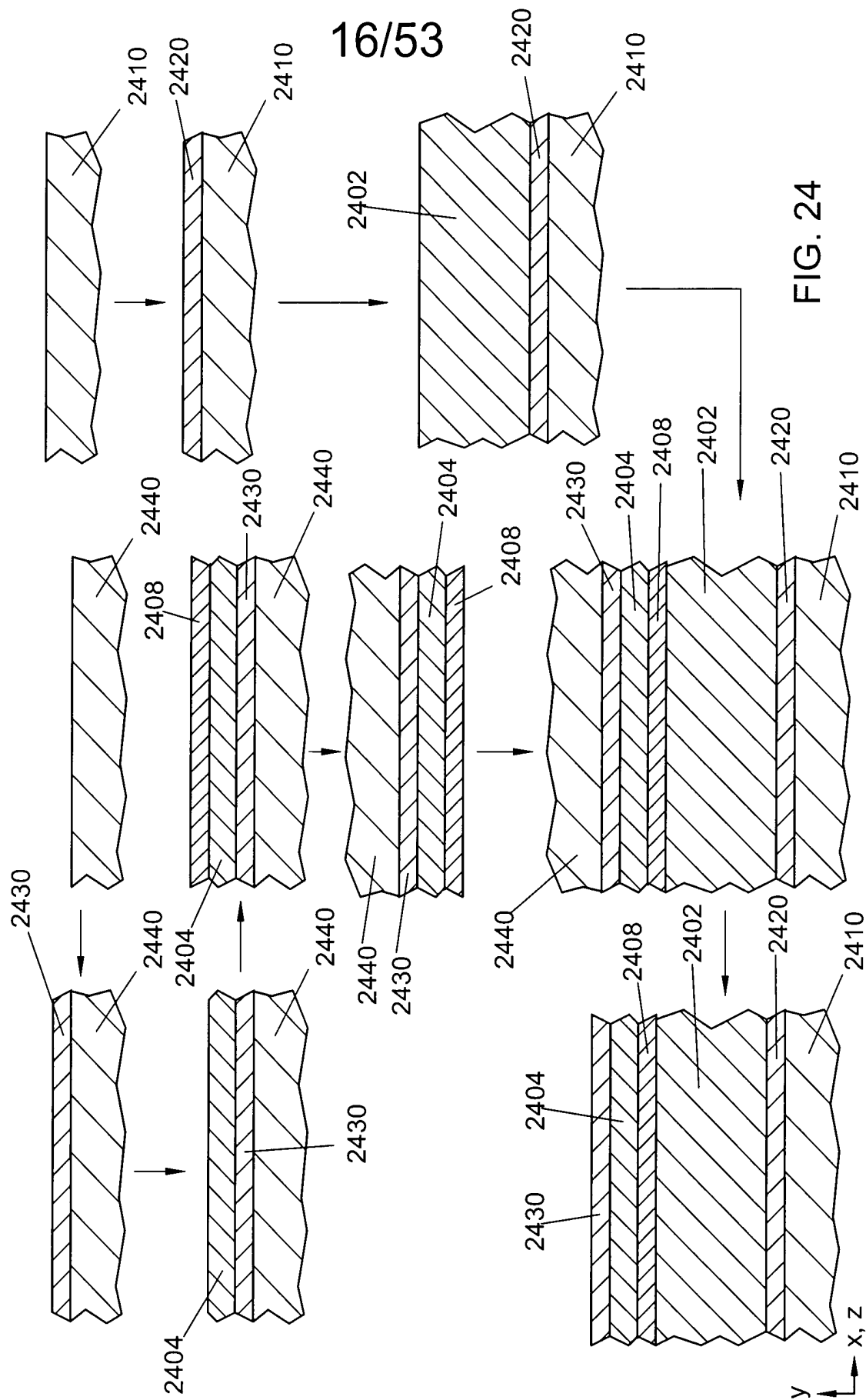


FIG. 24



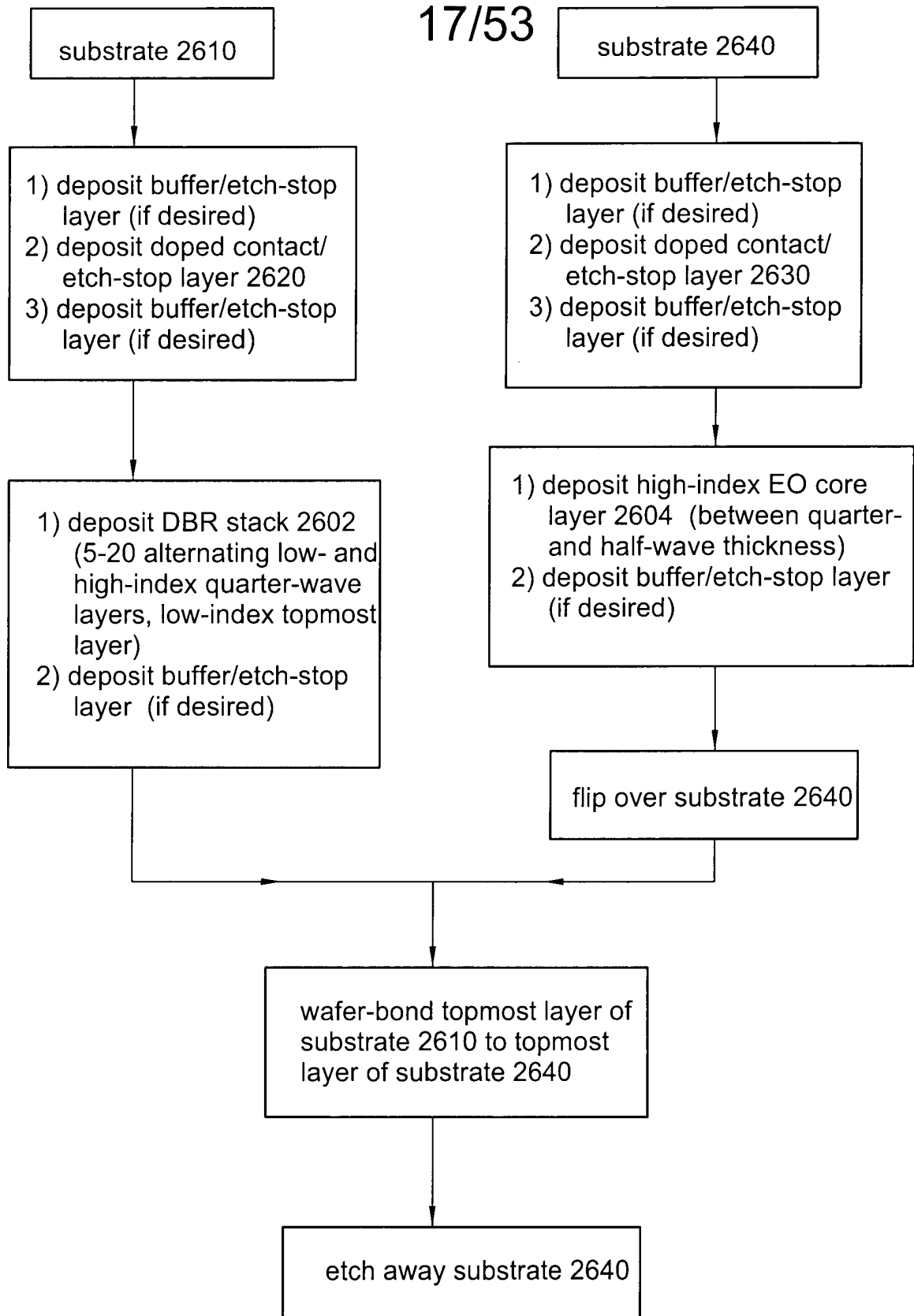


FIG. 25

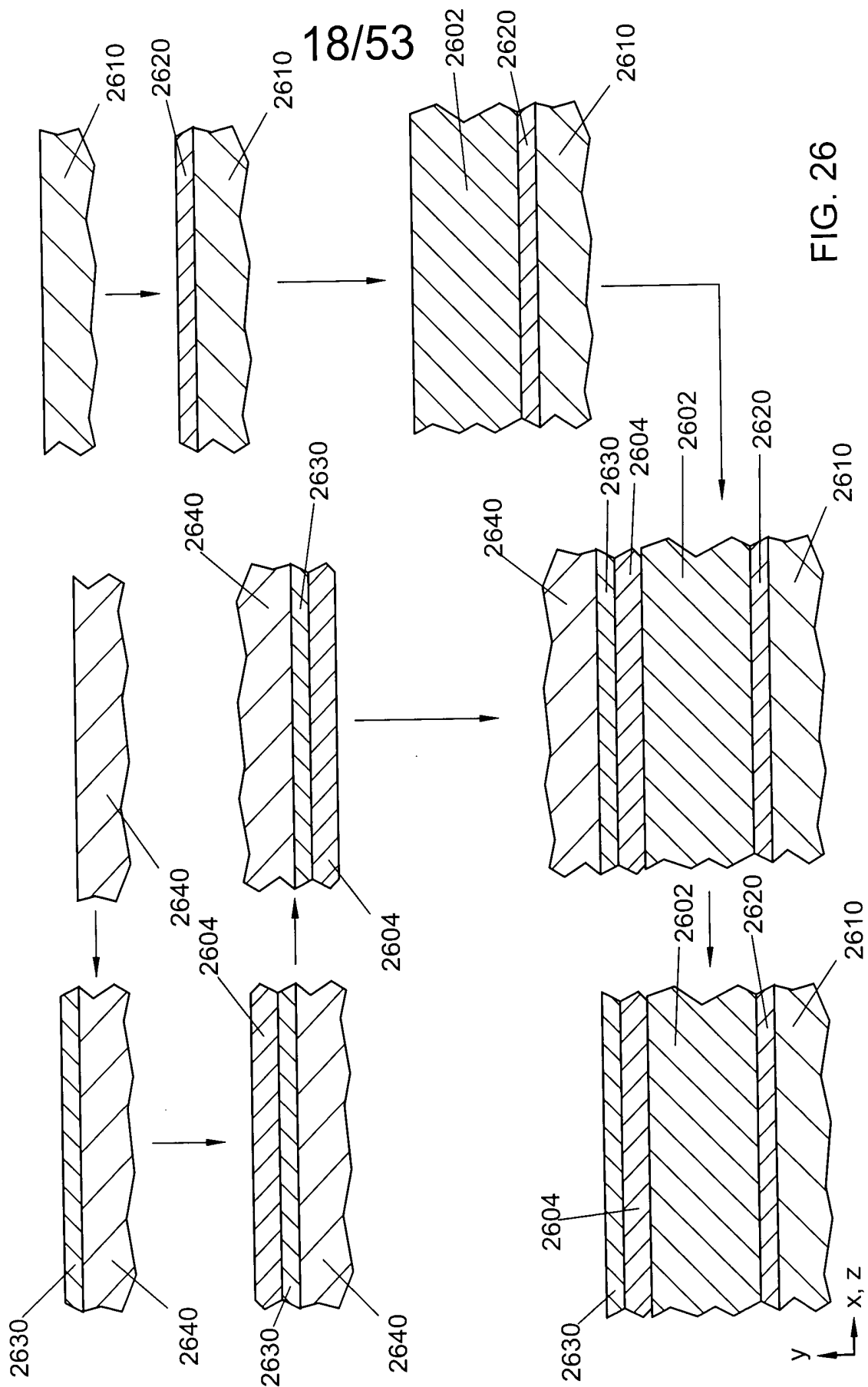


FIG. 26

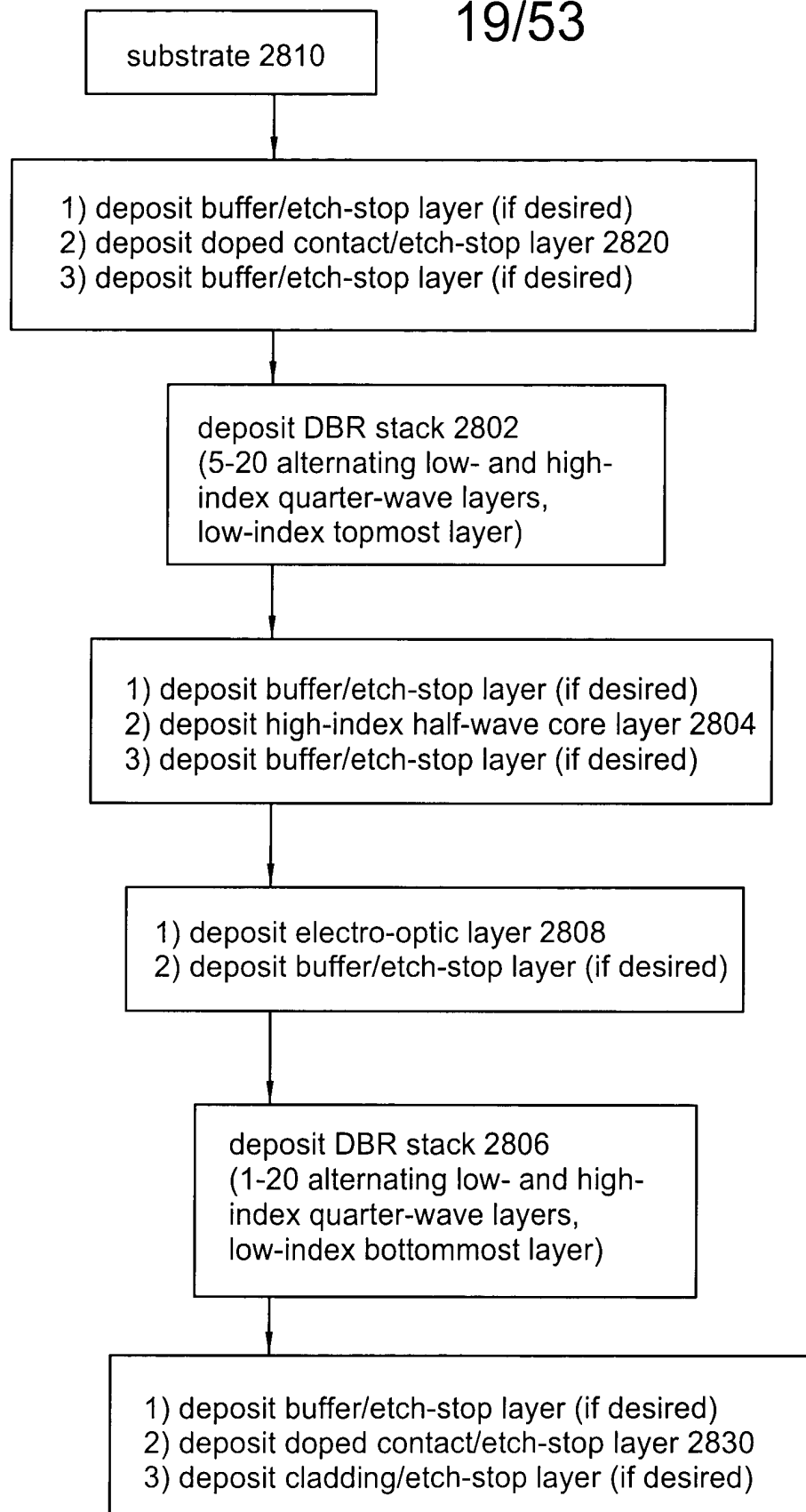
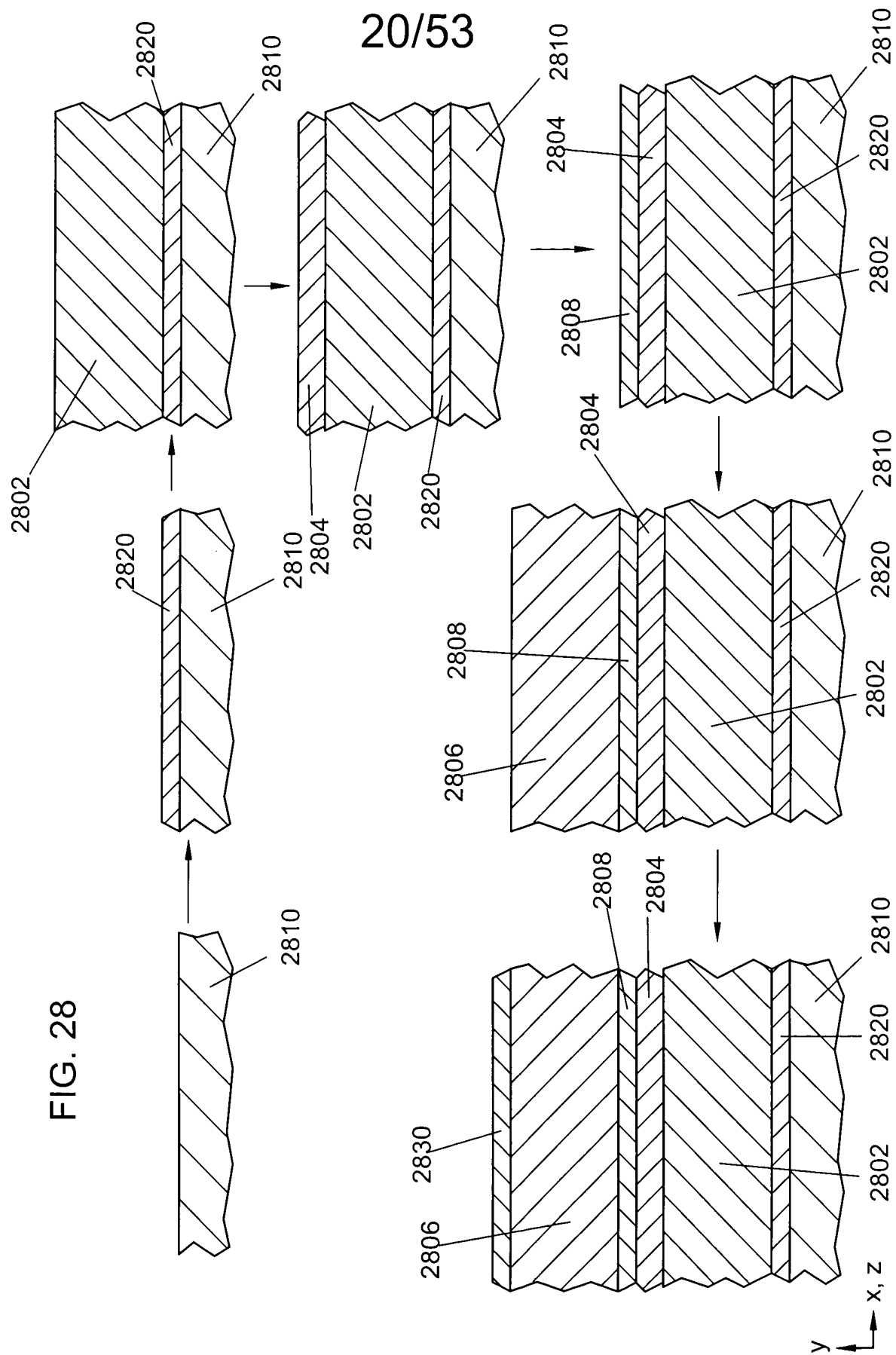


FIG. 27



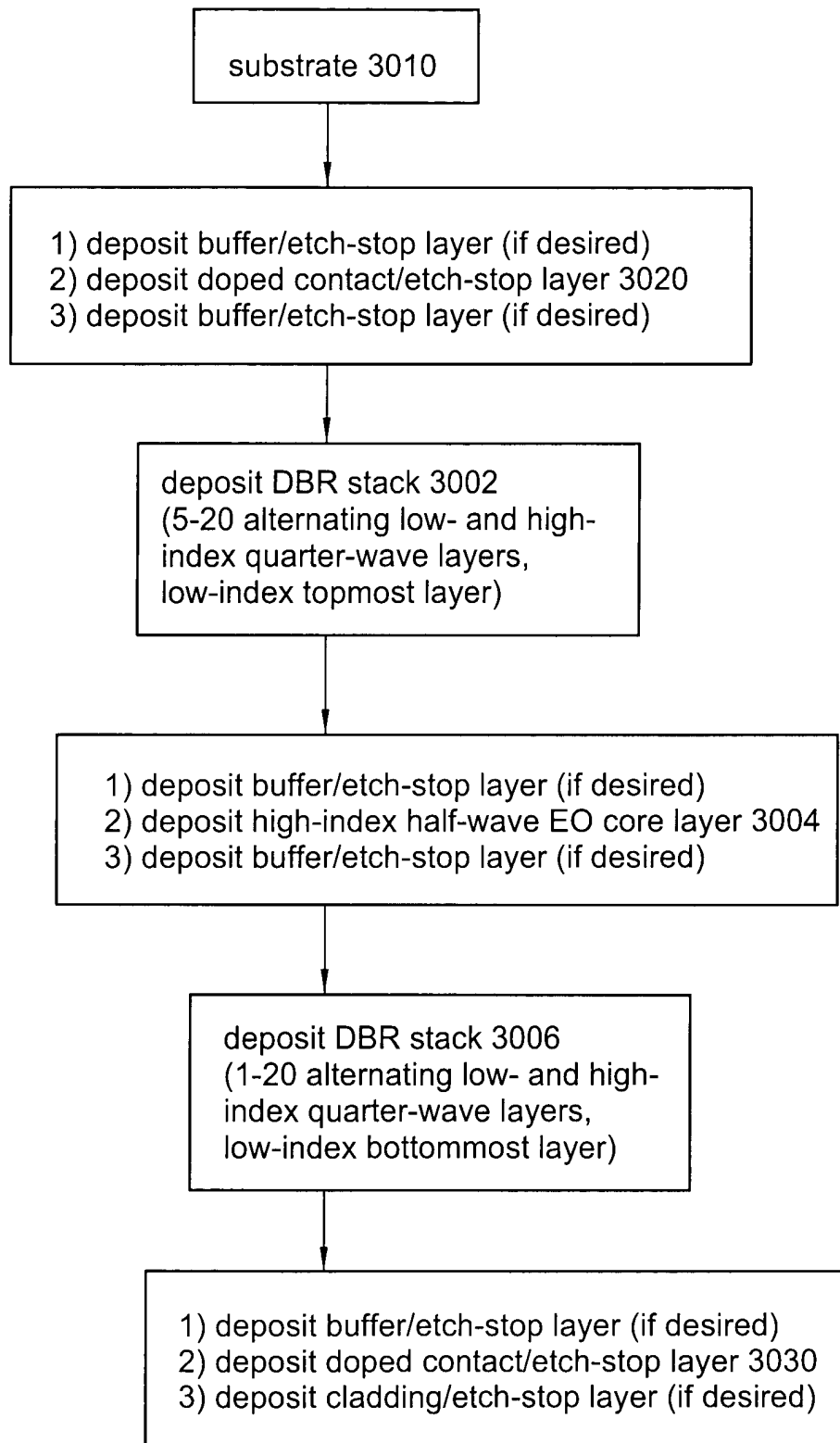
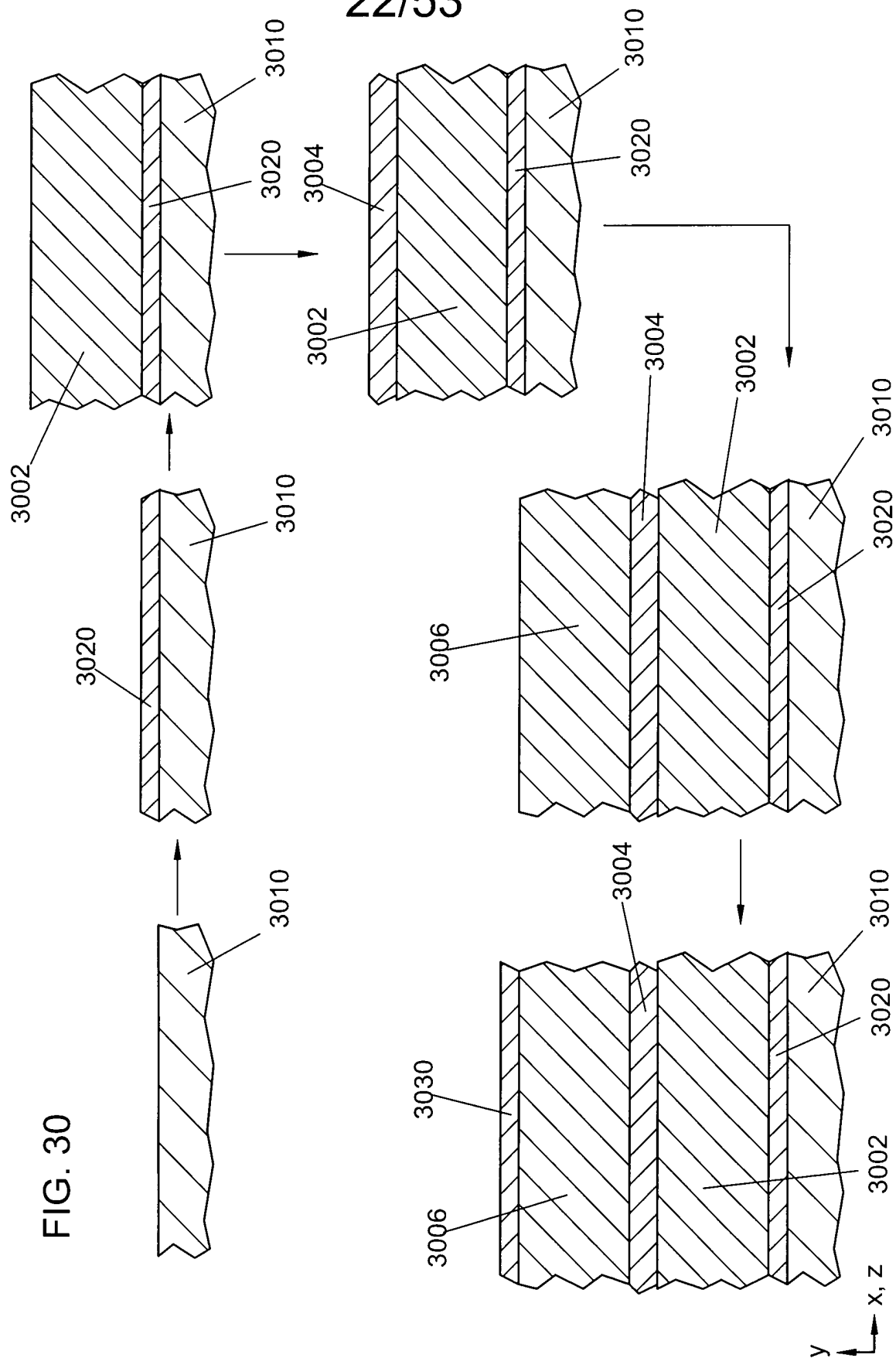


FIG. 29

FIG. 30



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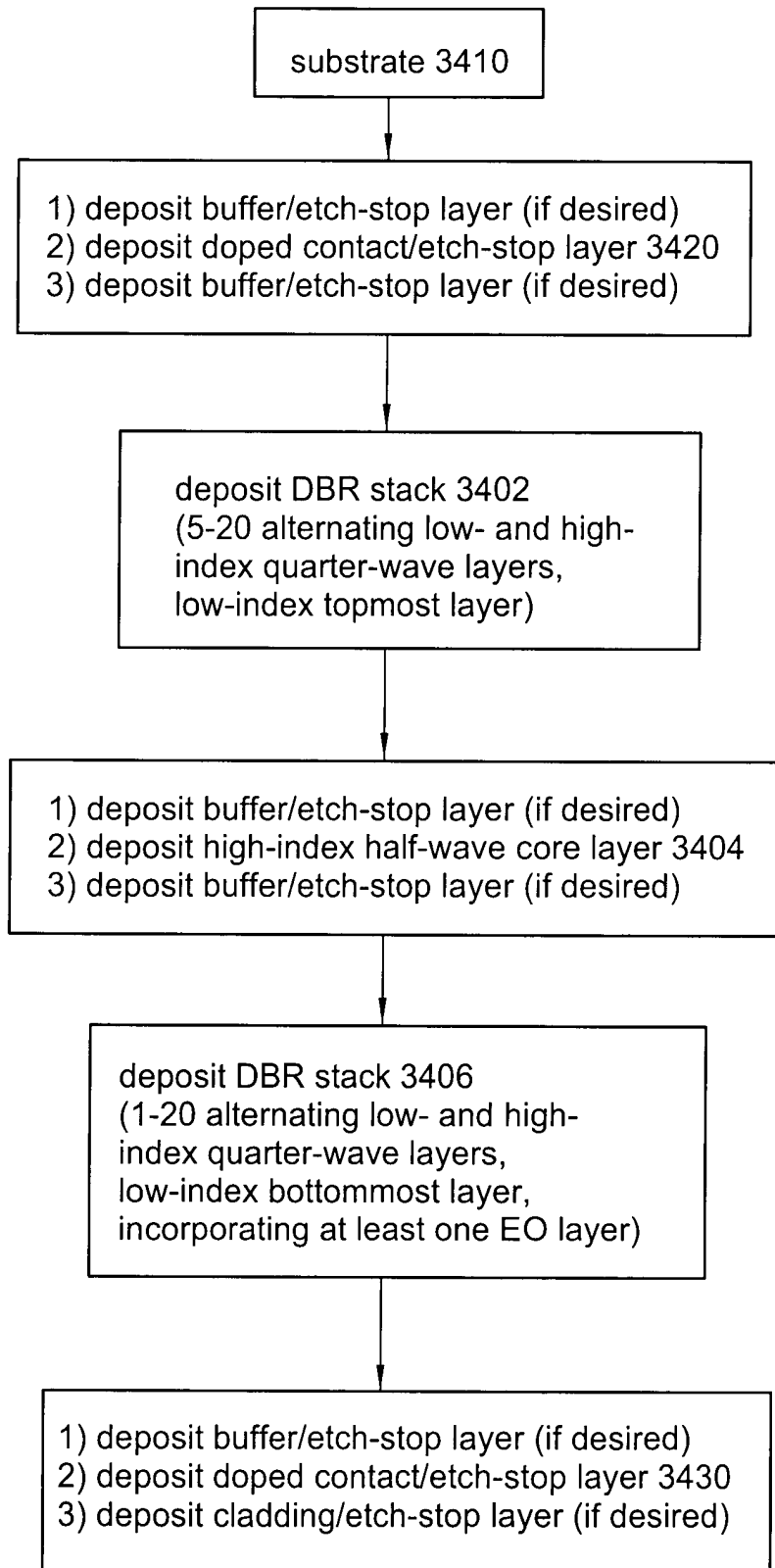


FIG. 31

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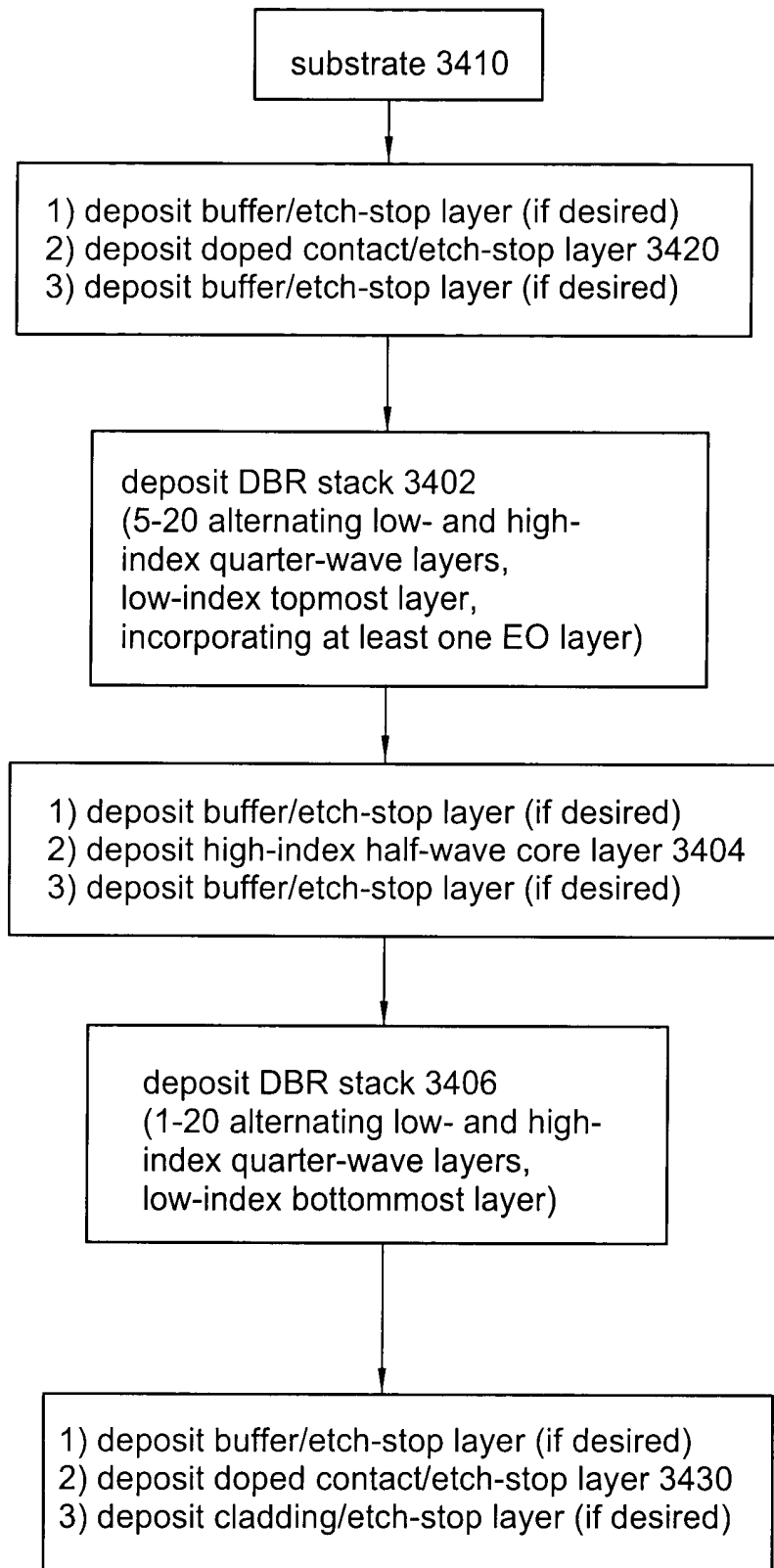


FIG. 32



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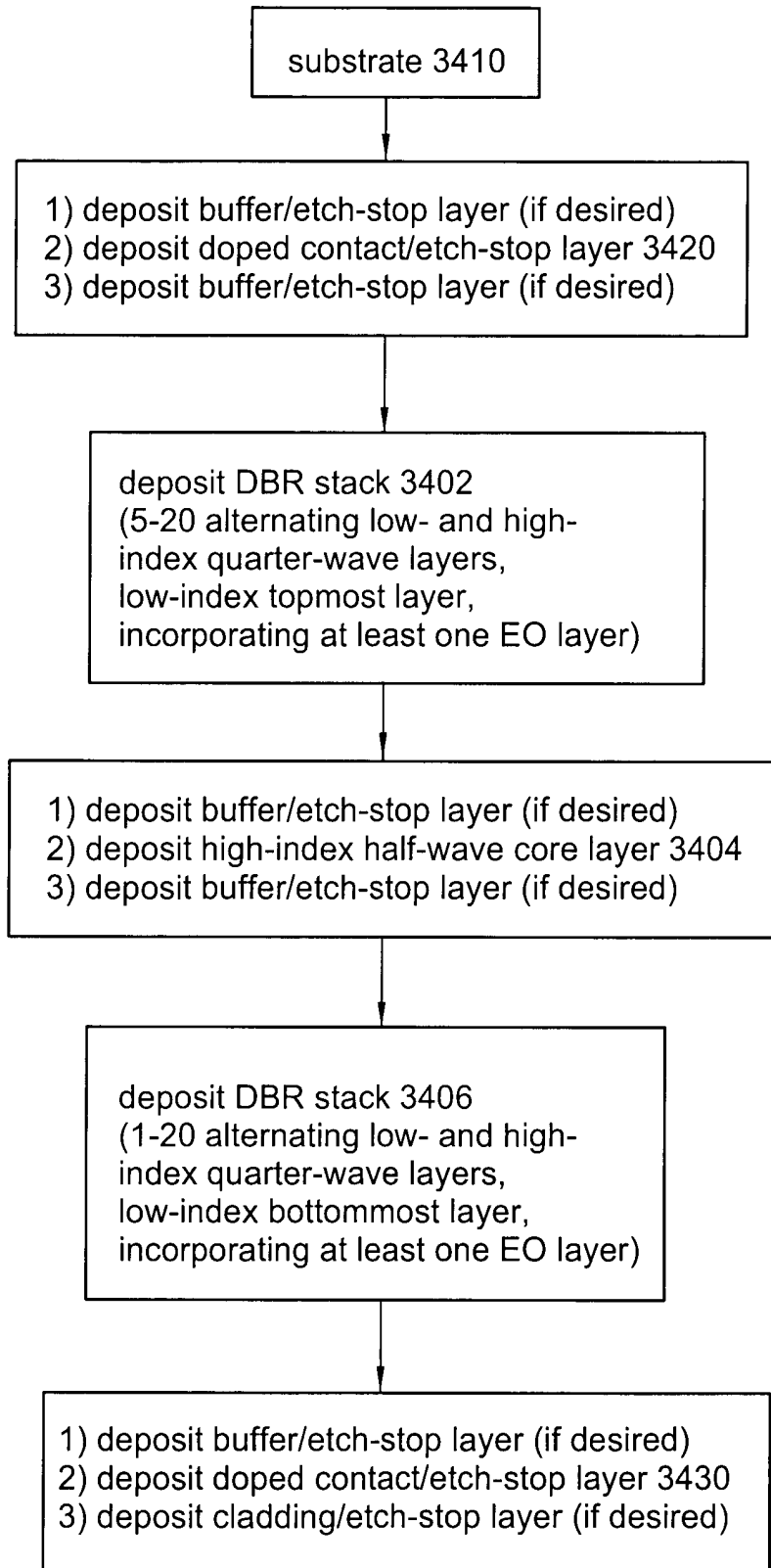
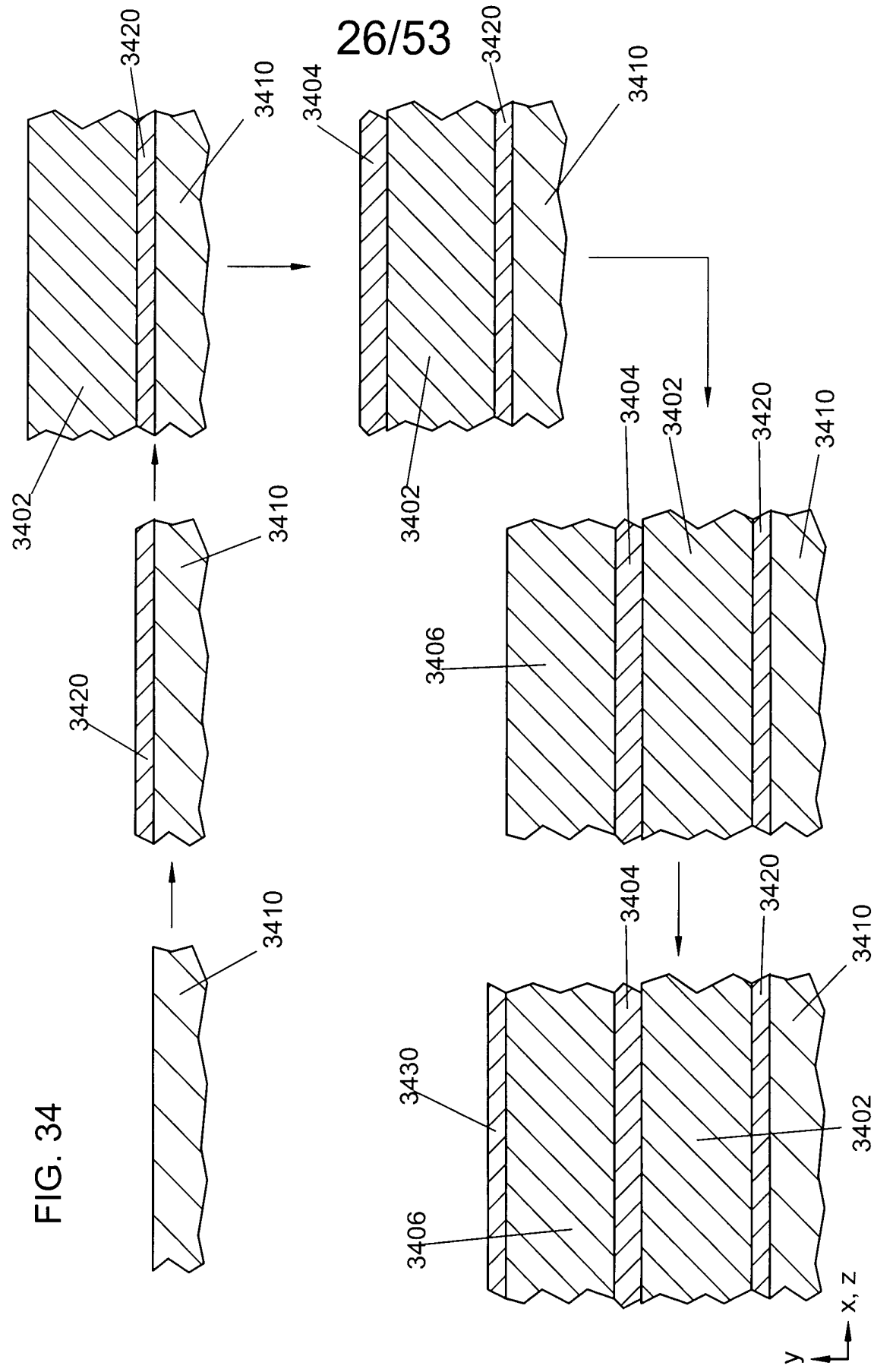


FIG. 33

FIG. 34 is a schematic diagram of a multi-layered structure 3400 in a cross-sectional view. The structure 3400 includes a substrate 3410 and a plurality of layers 3402, 3404, 3406, and 3430. The layers 3402, 3404, and 3406 are stacked on top of the substrate 3410. The layer 3430 is a thin layer located between the substrate 3410 and the layer 3402. The layers 3402, 3404, and 3406 have a wavy, undulating top surface. The layer 3430 has a flat top surface. The substrate 3410 has a flat bottom surface. The structure 3400 is shown in a cross-sectional view along the Y-Z plane, with the X-axis pointing out of the page. The layers 3402, 3404, and 3406 are made of a material with a different dielectric constant than the substrate 3410 and the layer 3430. The layers 3402, 3404, and 3406 are used to provide a specific electrical property to the structure 3400. The layer 3430 is used to provide a specific electrical property to the structure 3400. The structure 3400 is used in a variety of applications, including as a component of a semiconductor device, a component of a microelectronic device, or a component of a MEMS device.

FIG. 34



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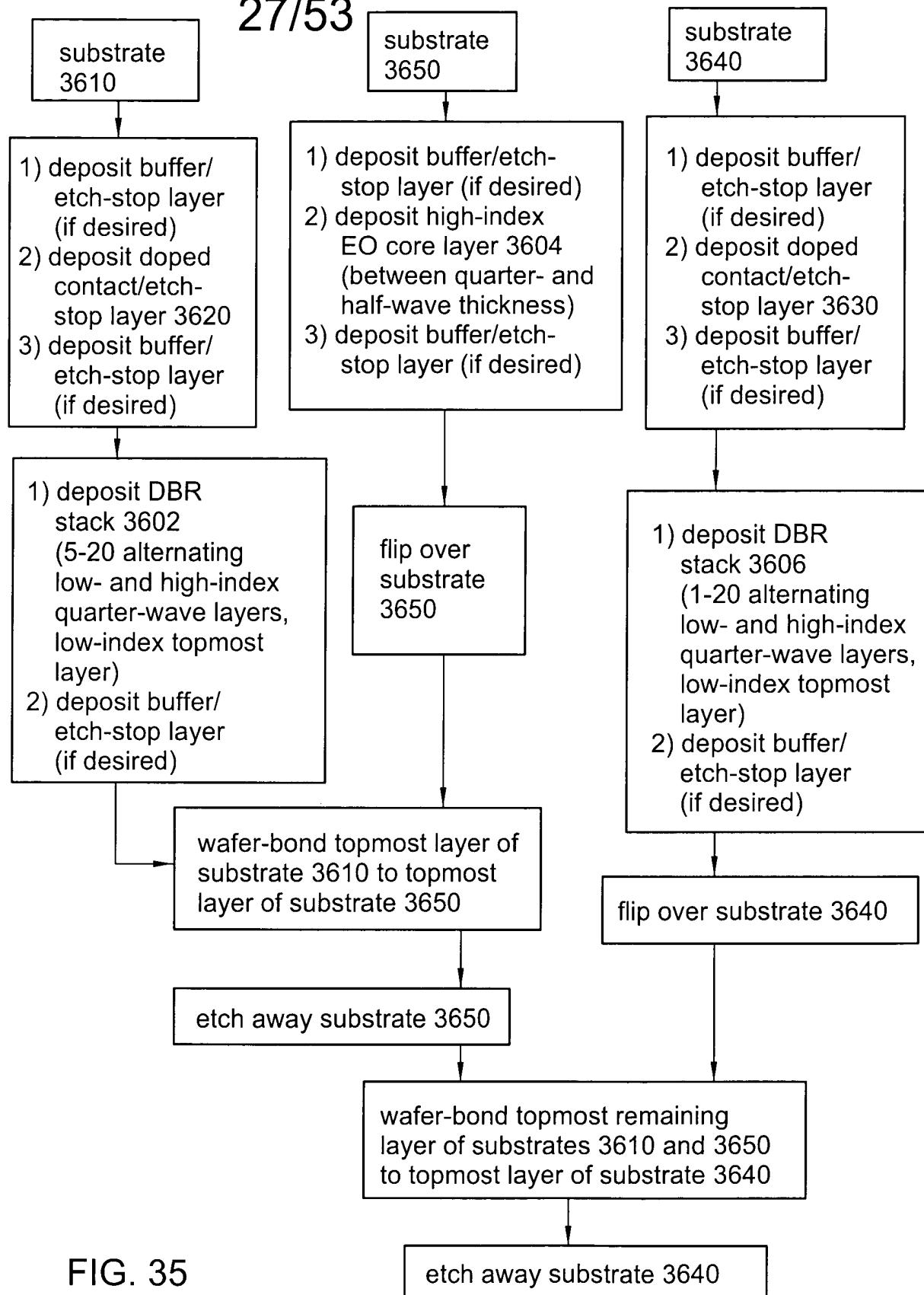
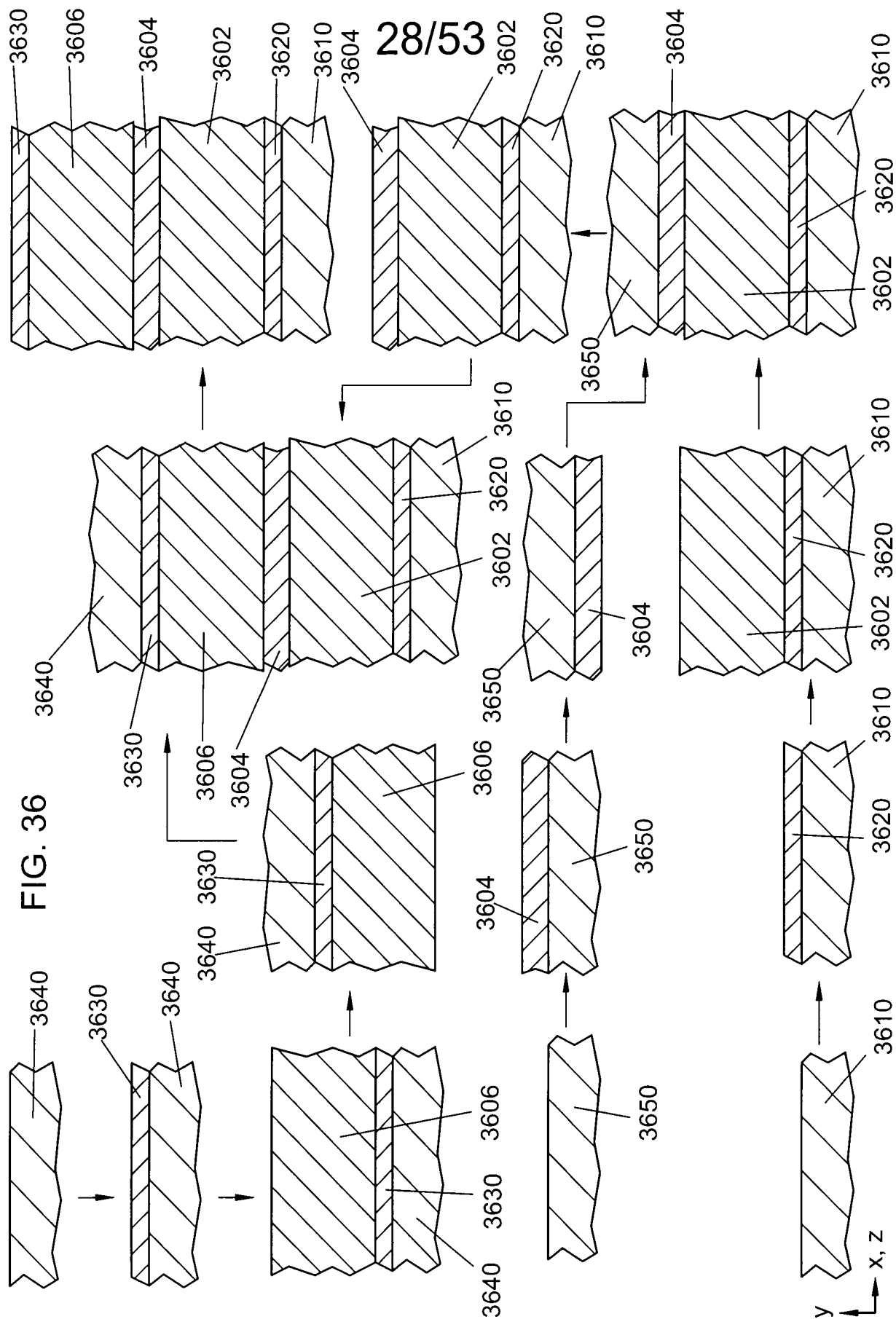


FIG. 35

FIG. 36



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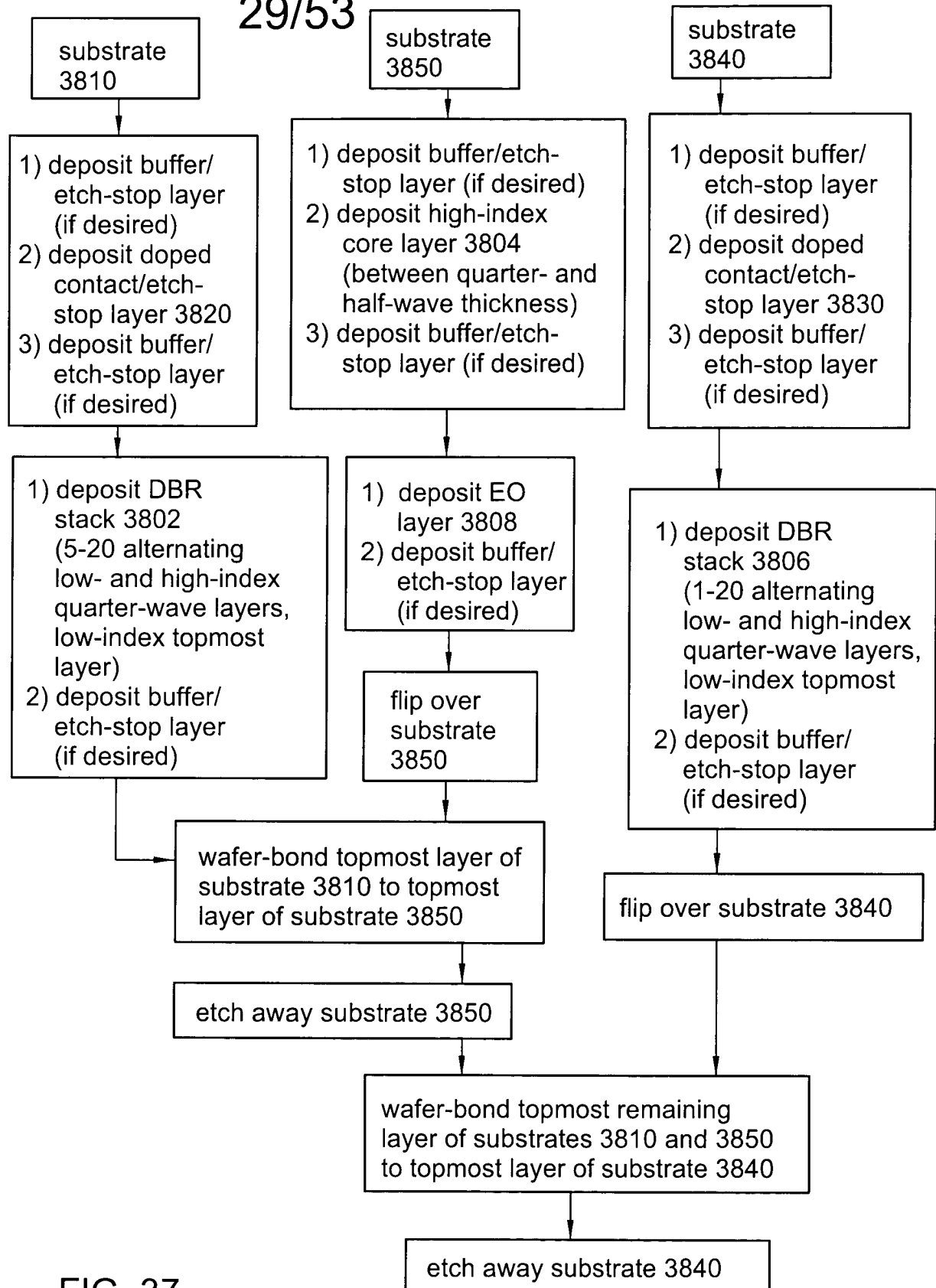
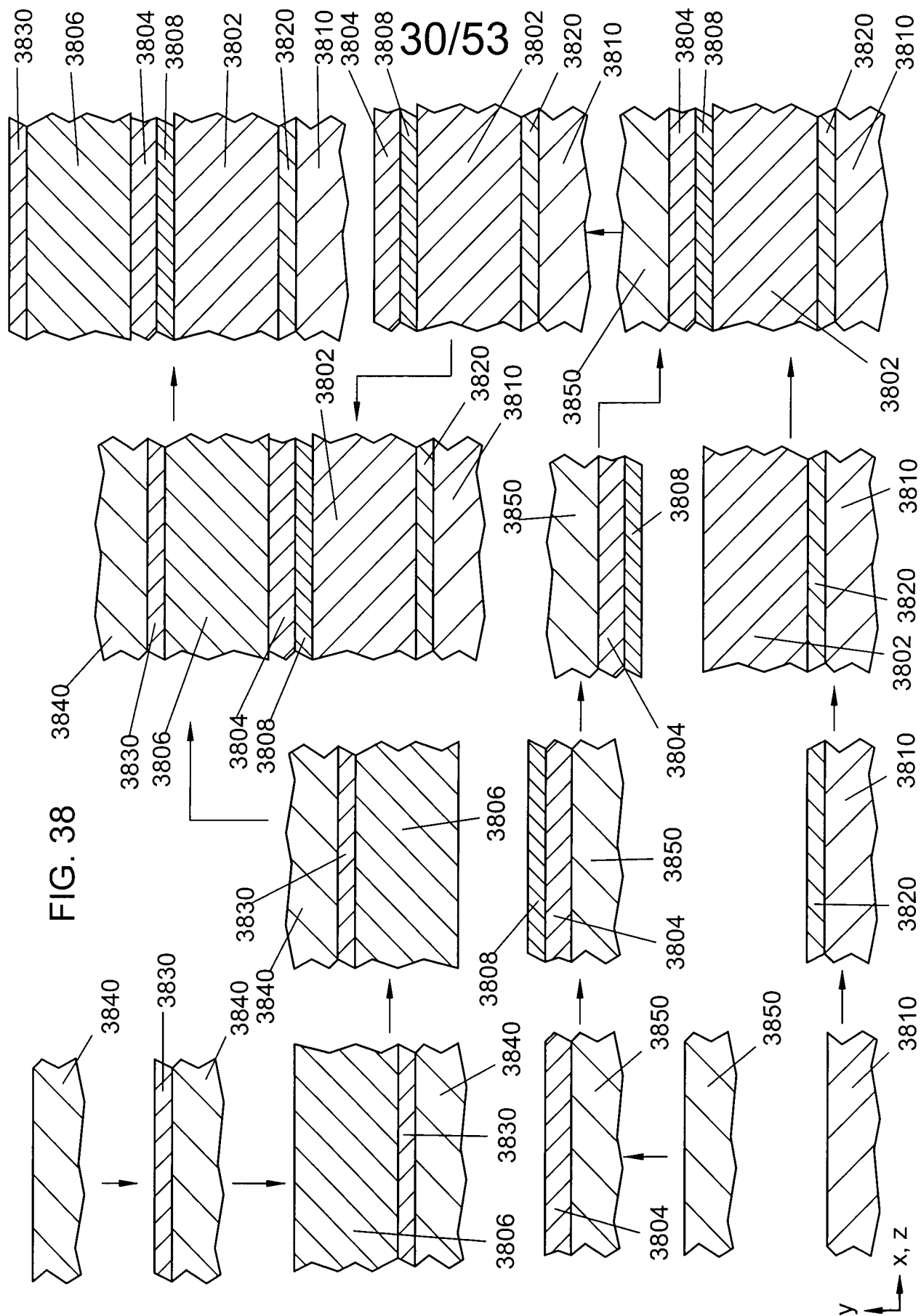


FIG. 37



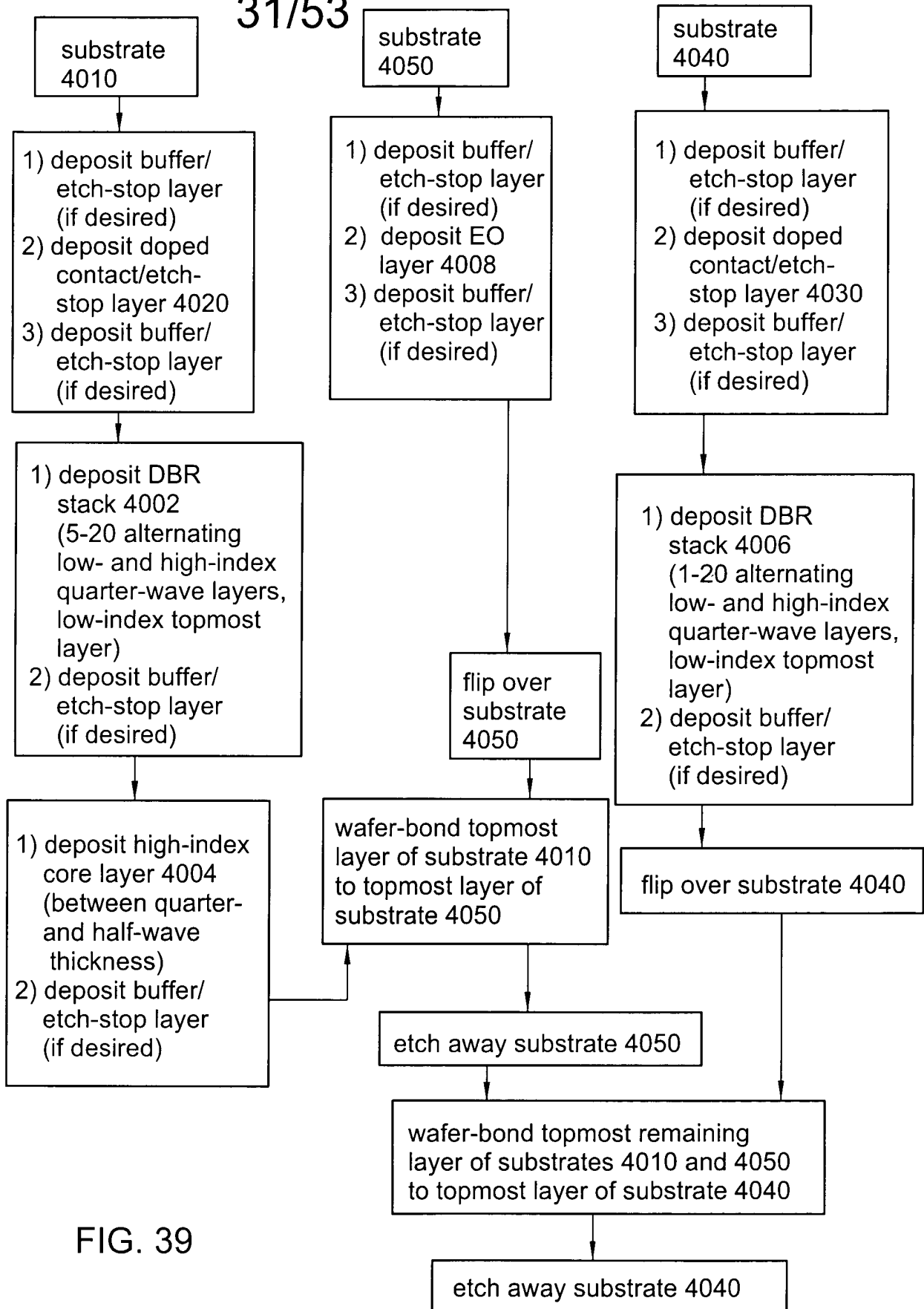
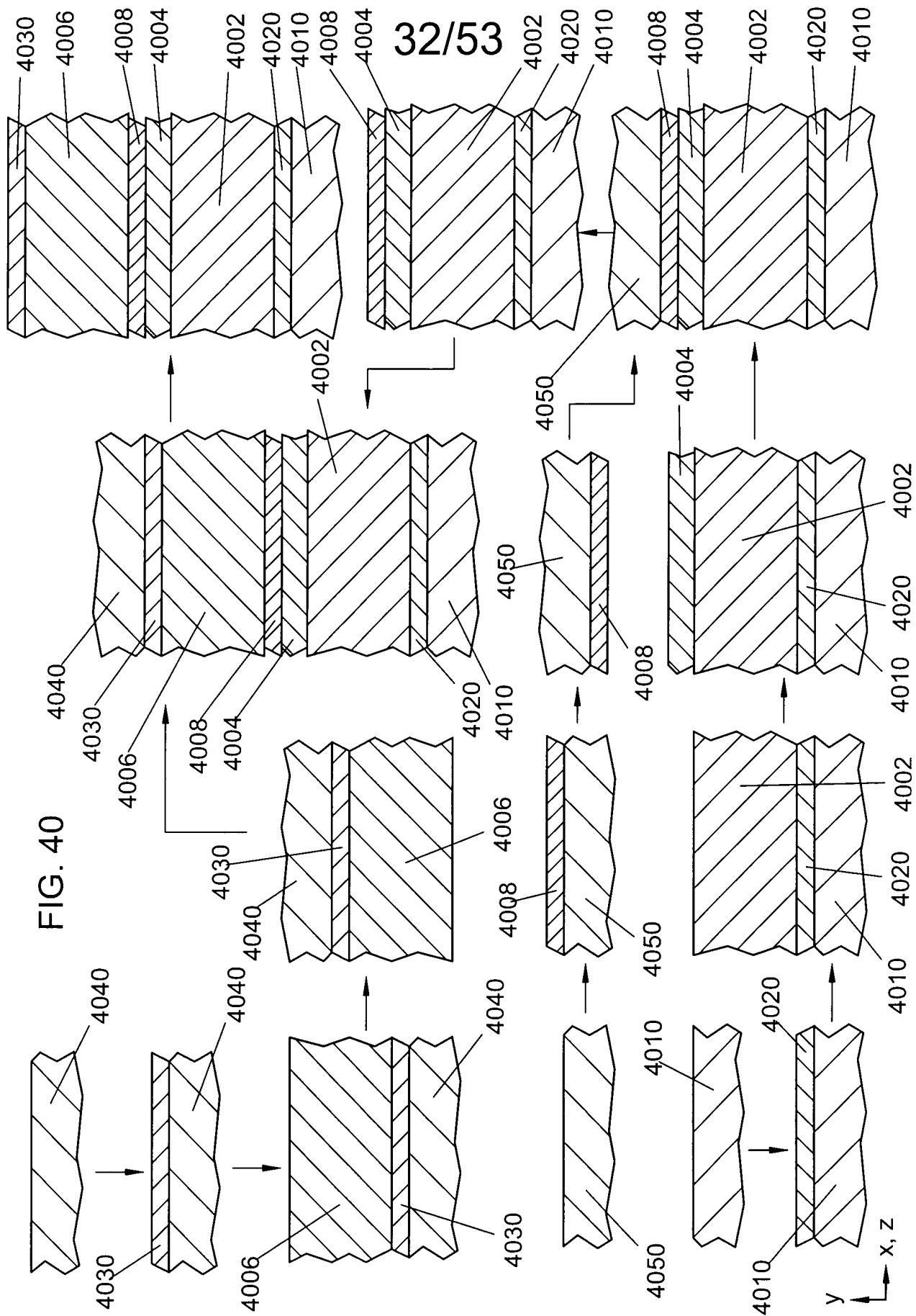


FIG. 39





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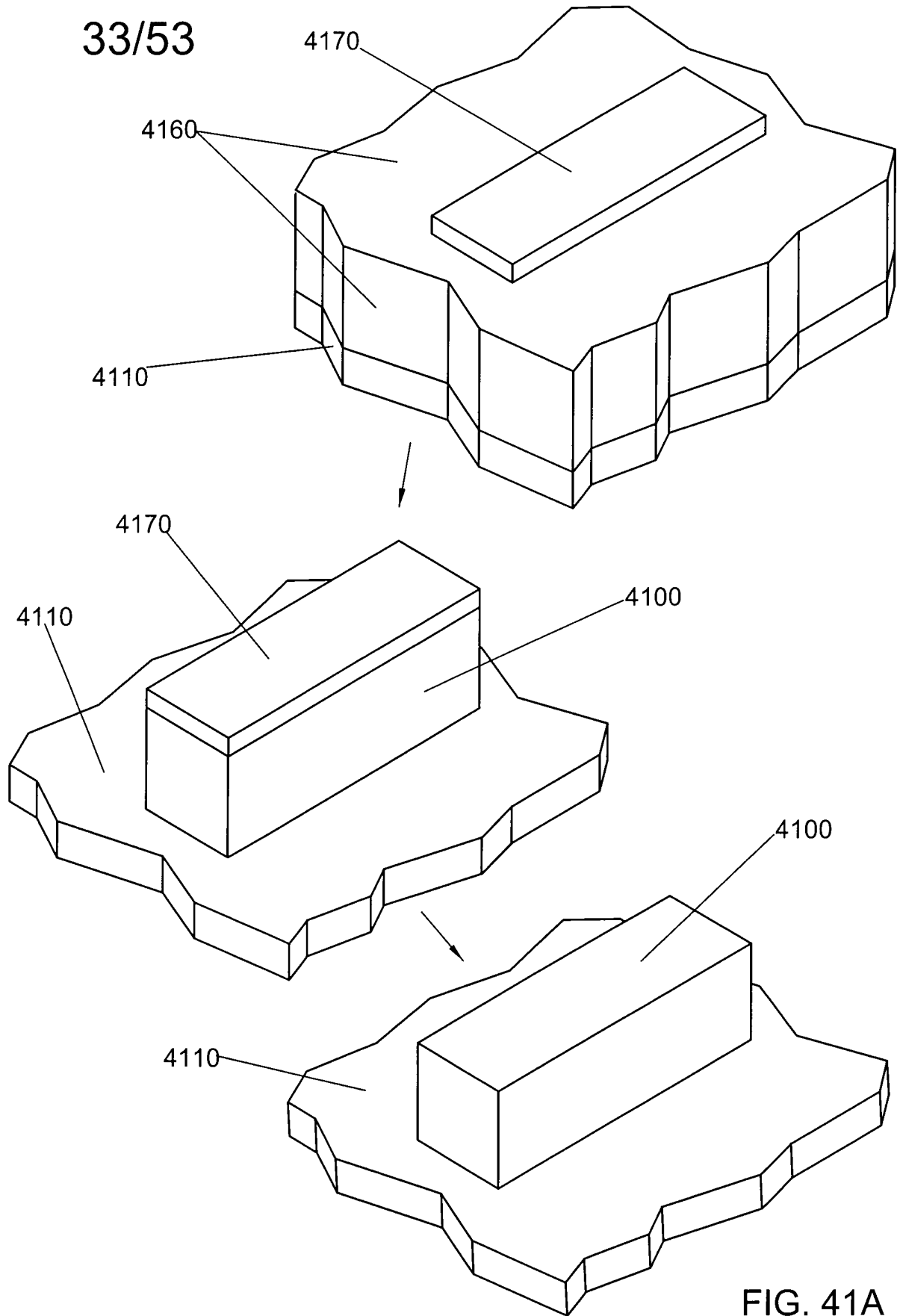


FIG. 41A

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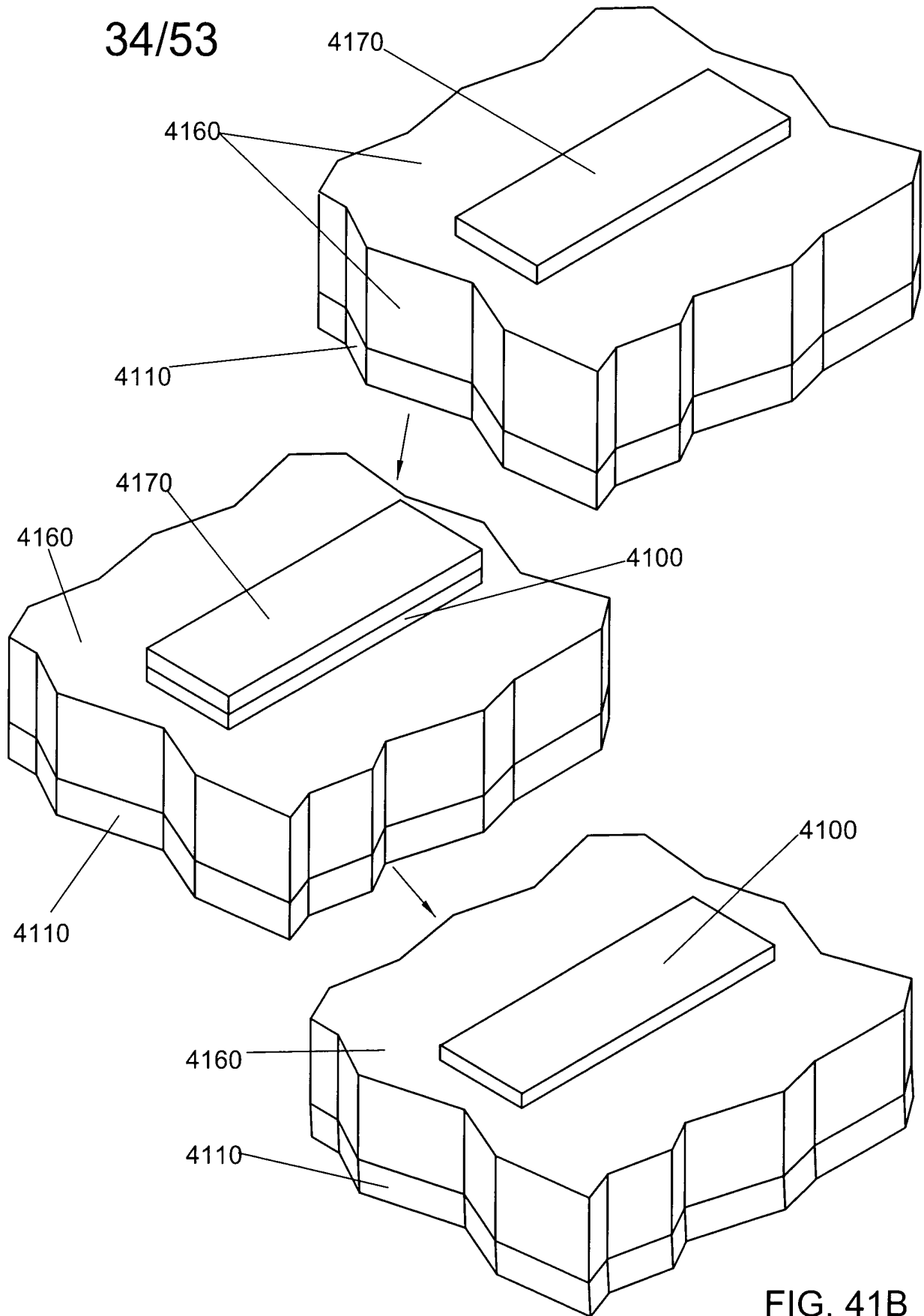


FIG. 41B

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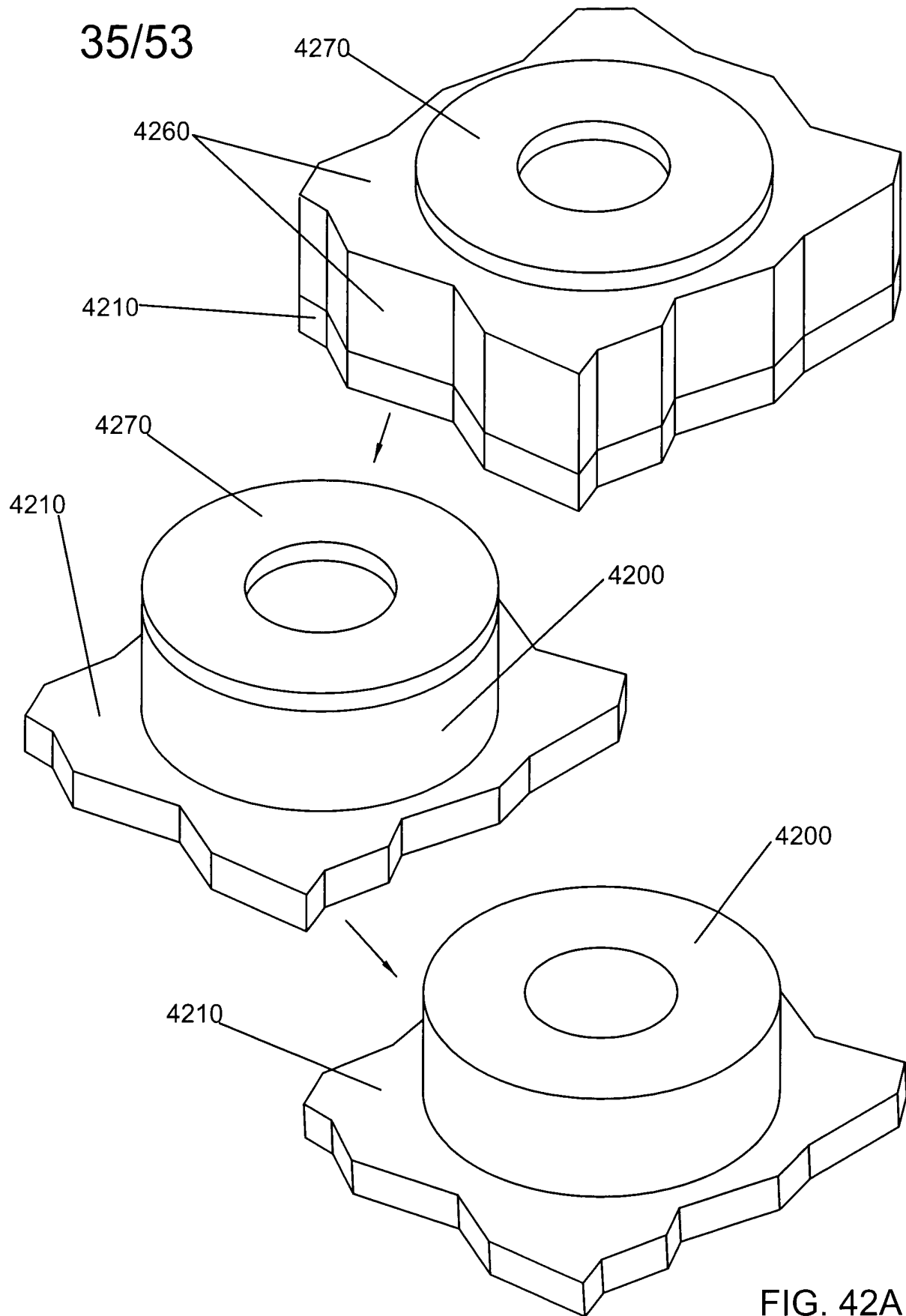


FIG. 42A

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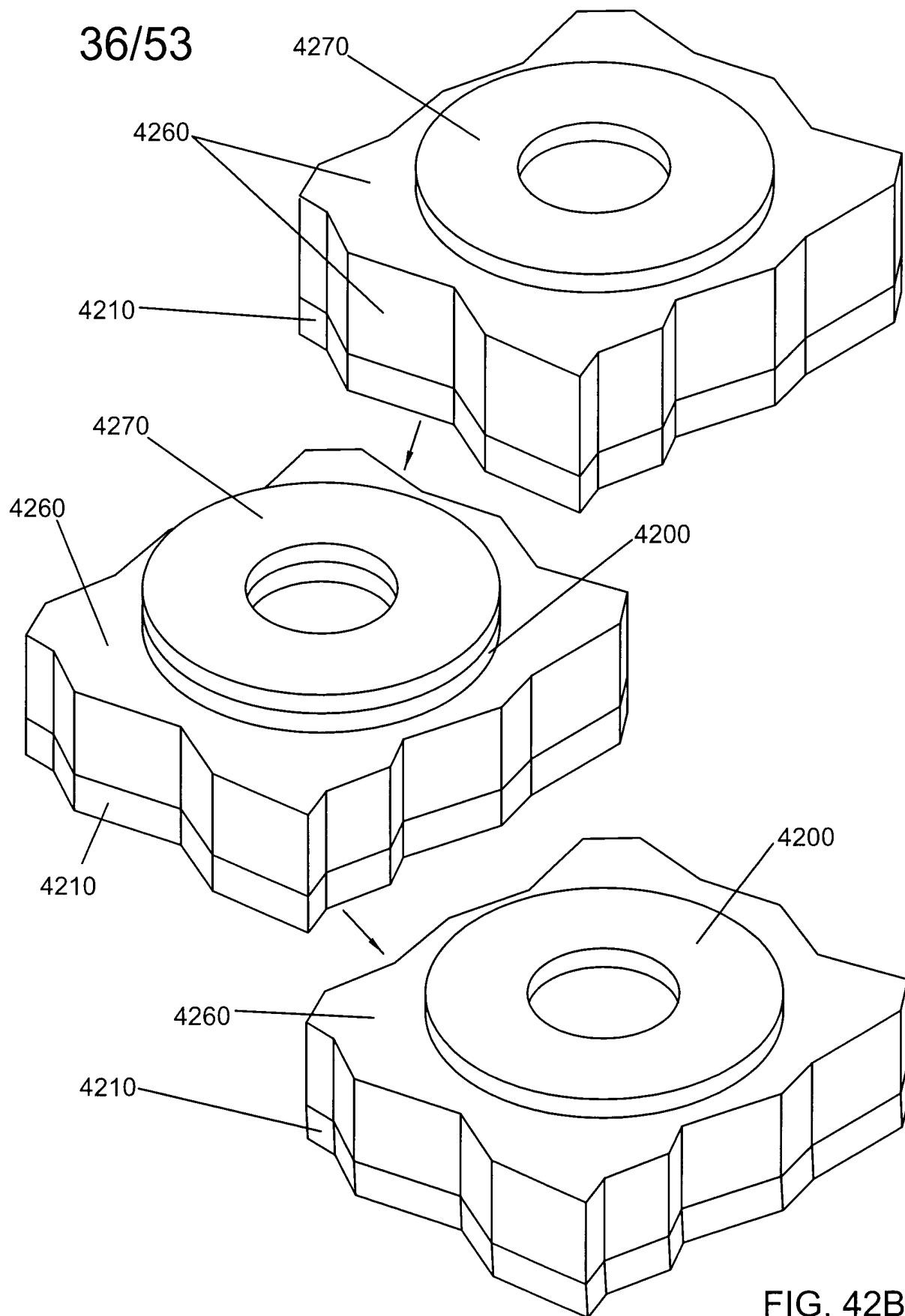


FIG. 42B

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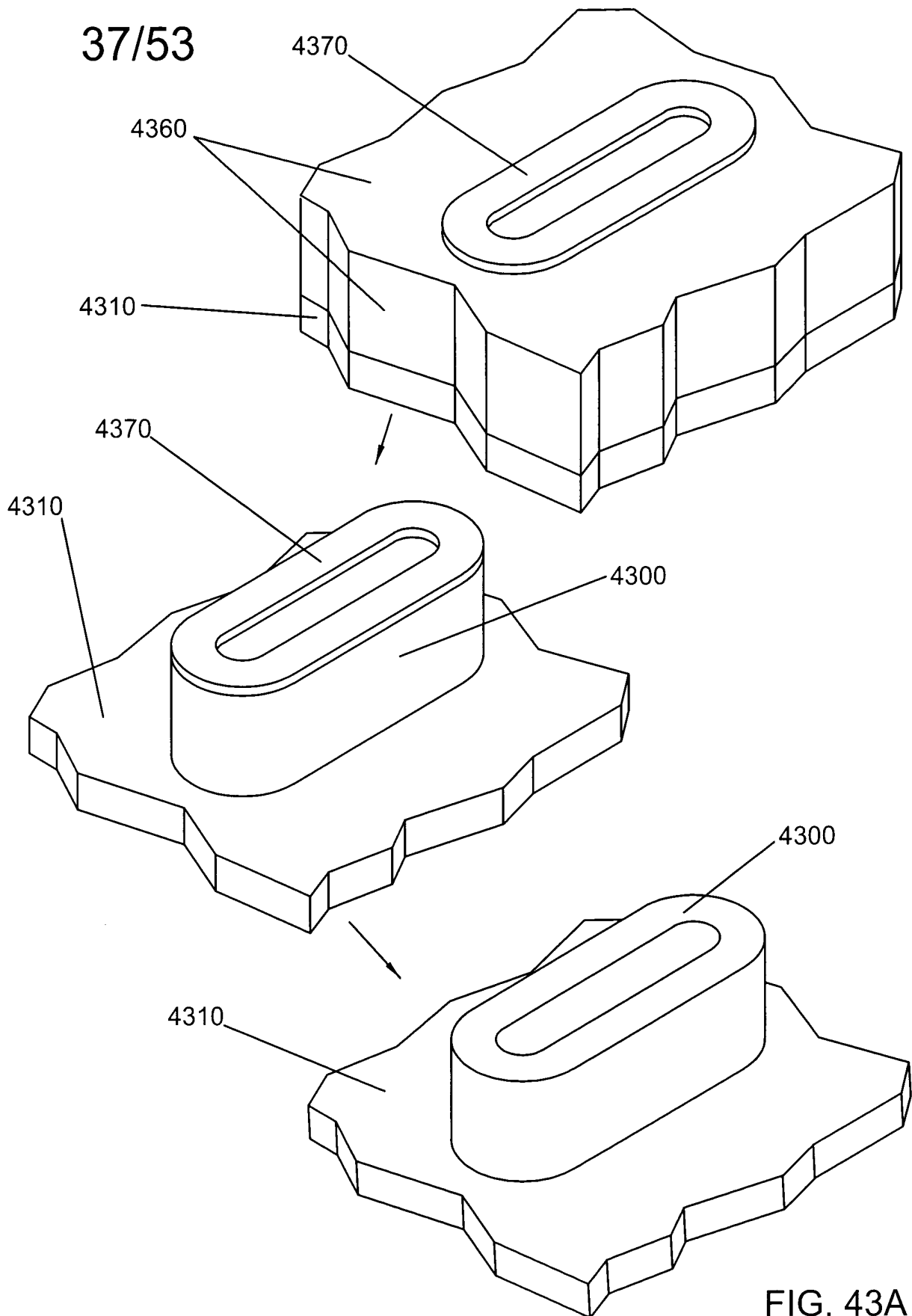


FIG. 43A

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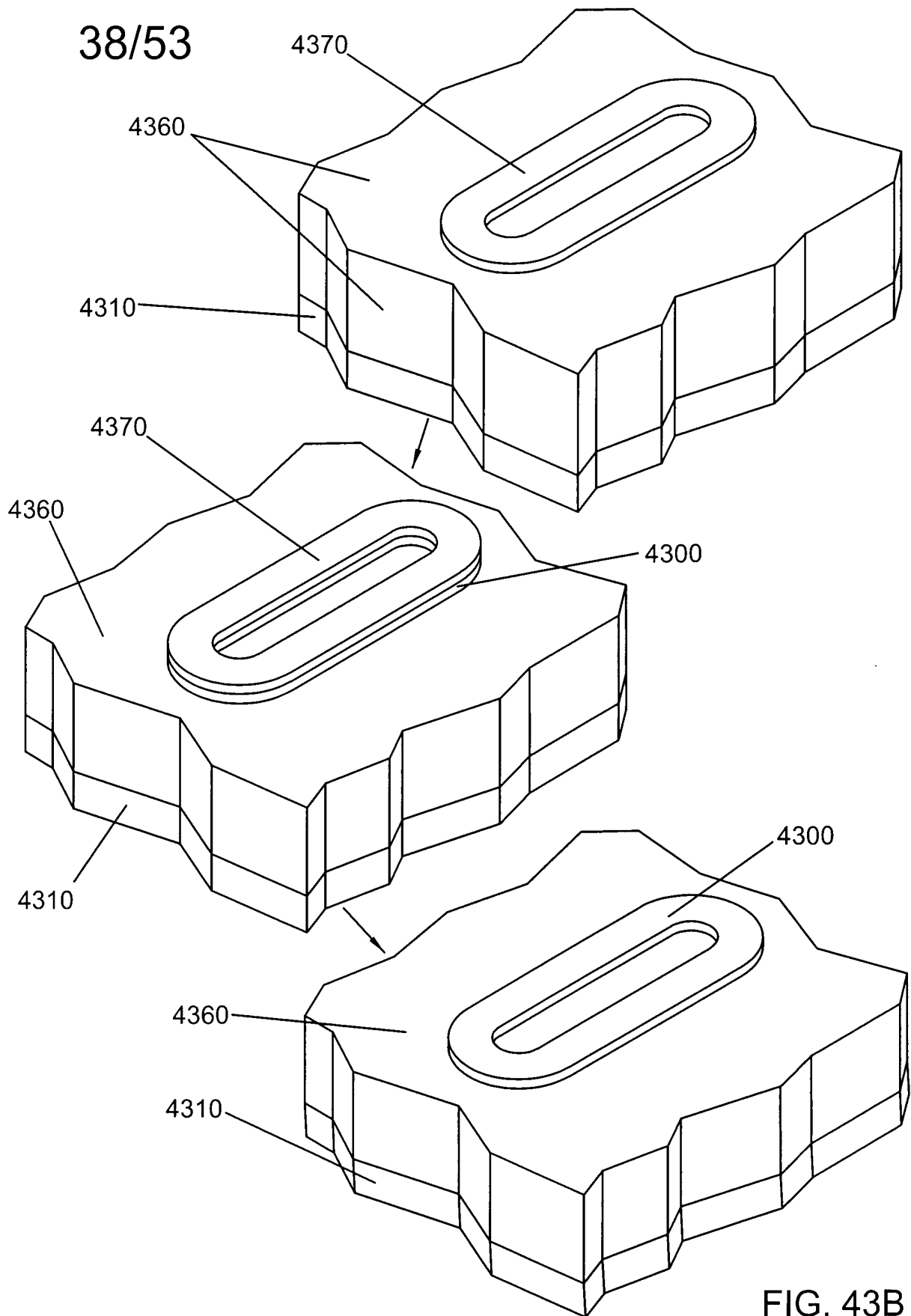


FIG. 43B

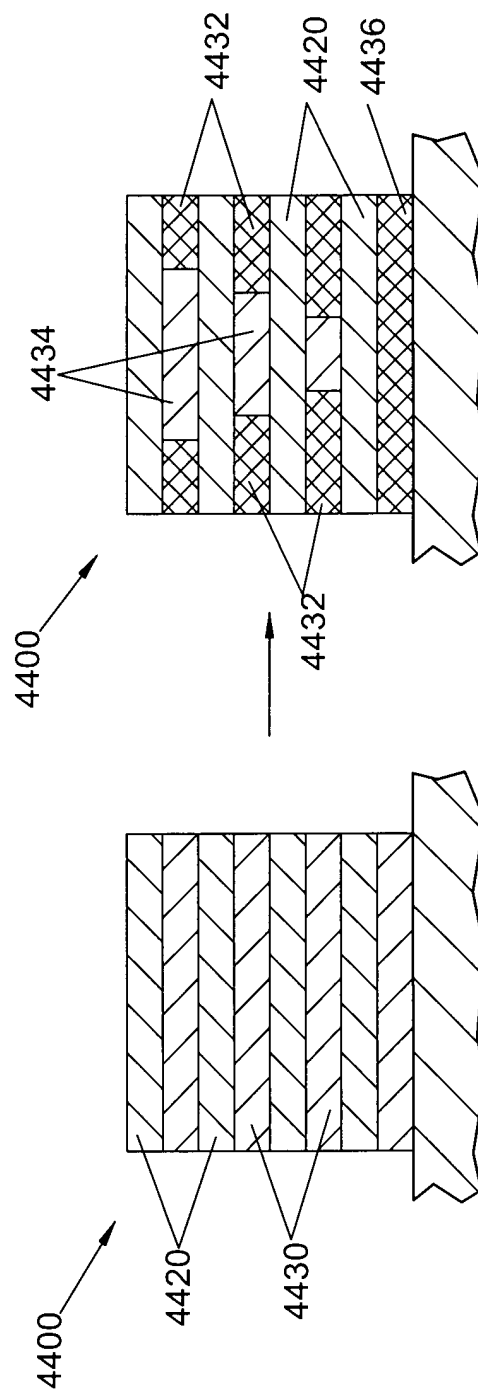
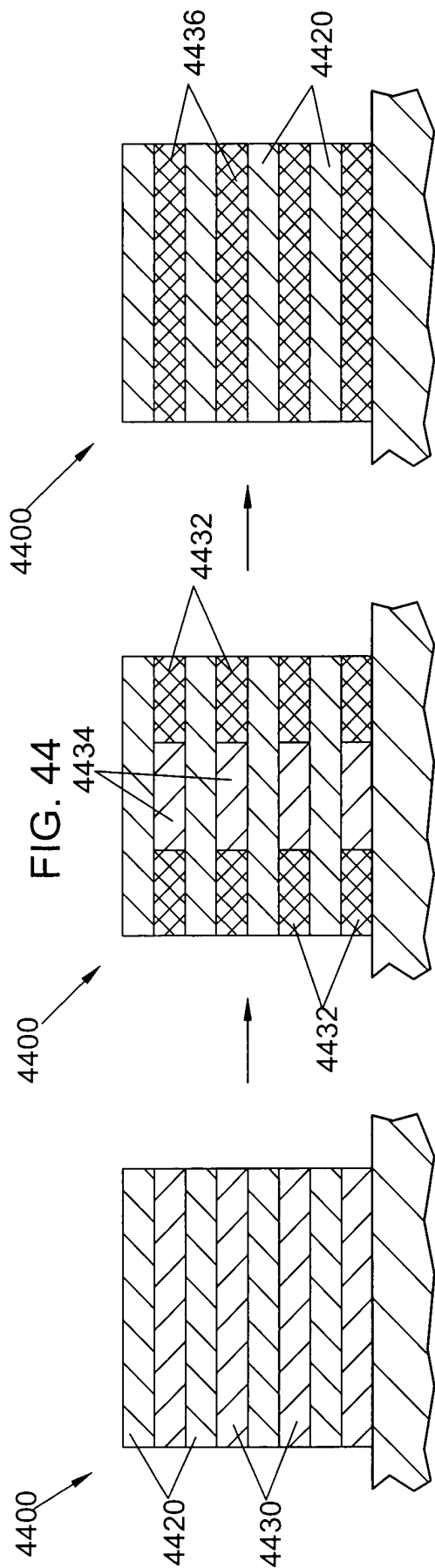


FIG. 46

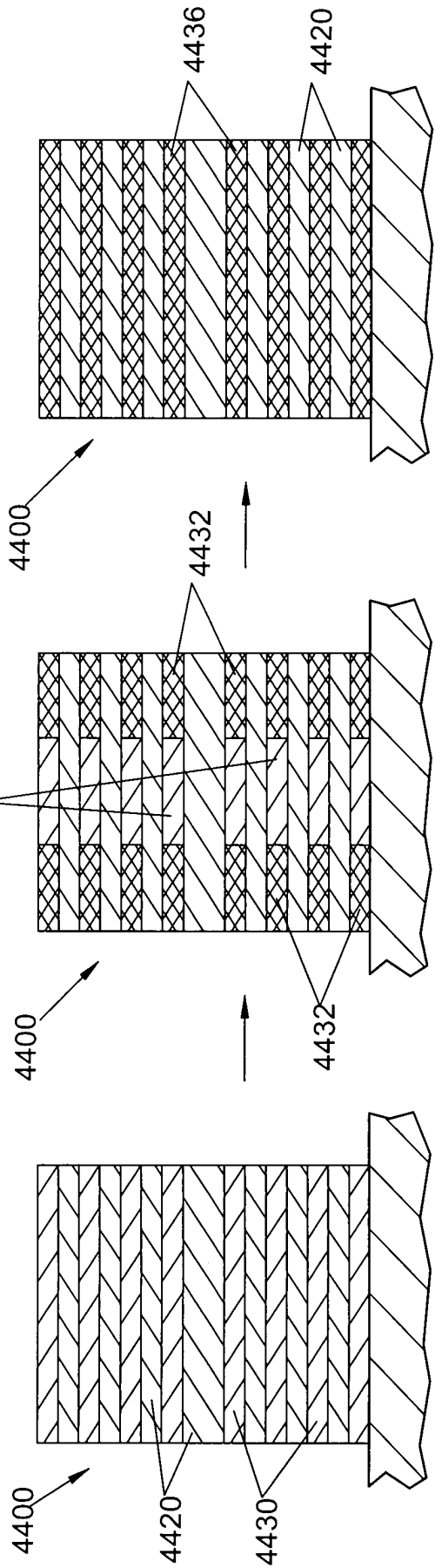


FIG. 47

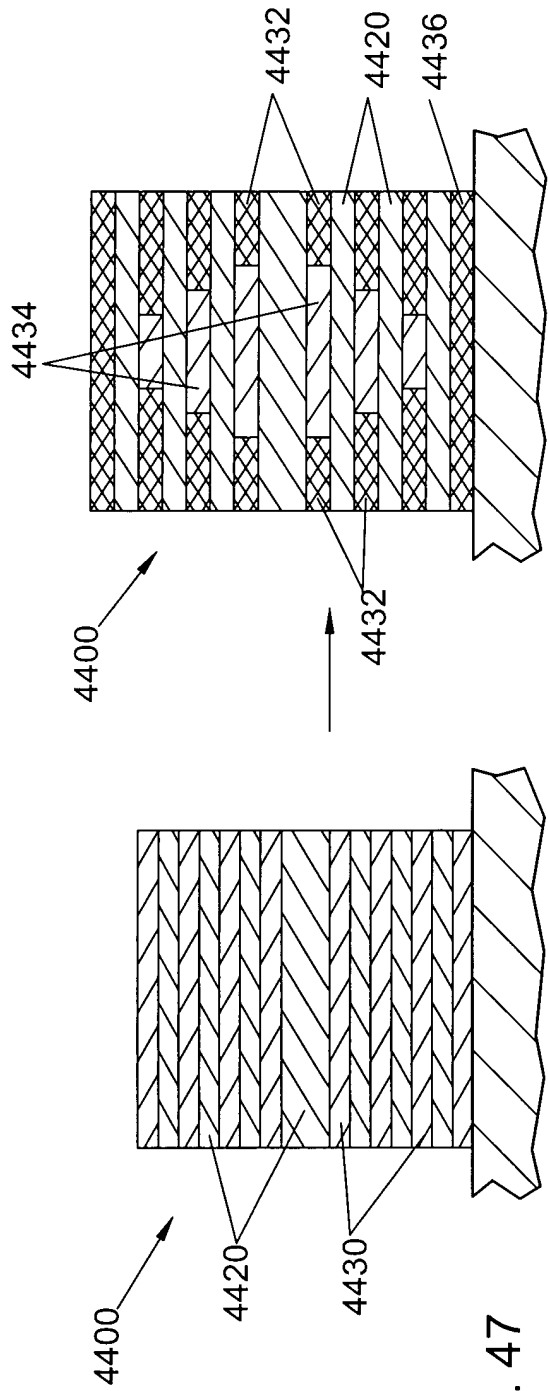




FIG. 48

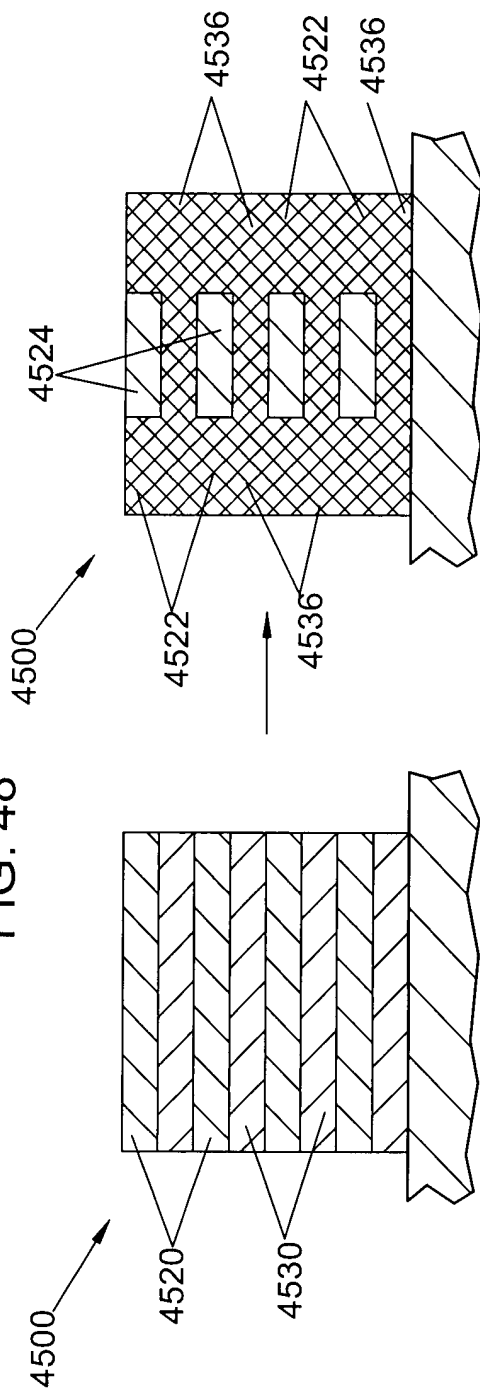


FIG. 49

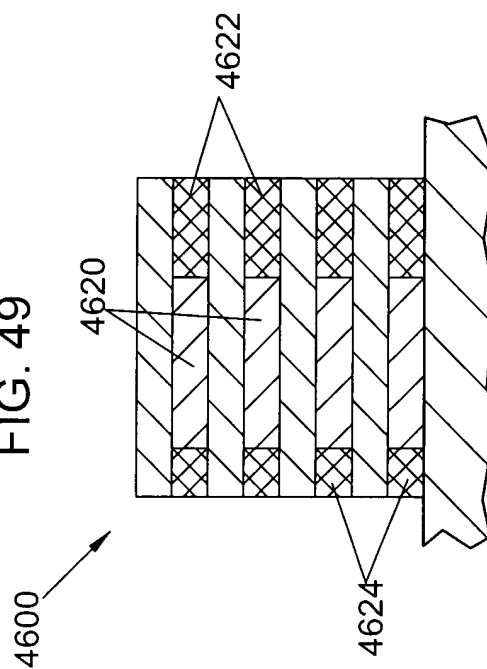
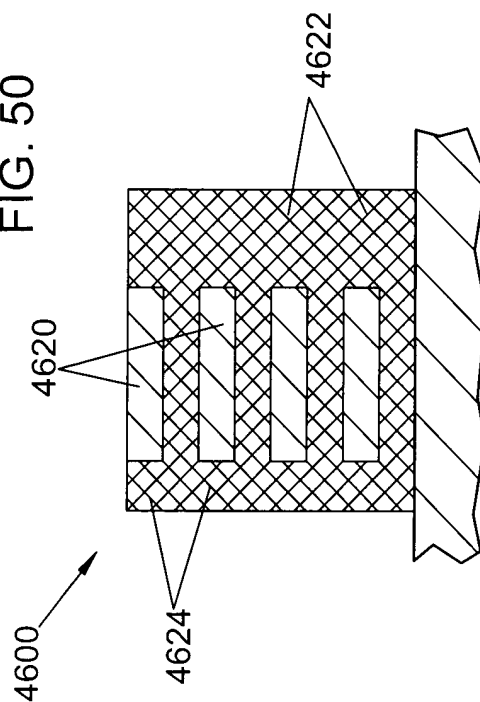
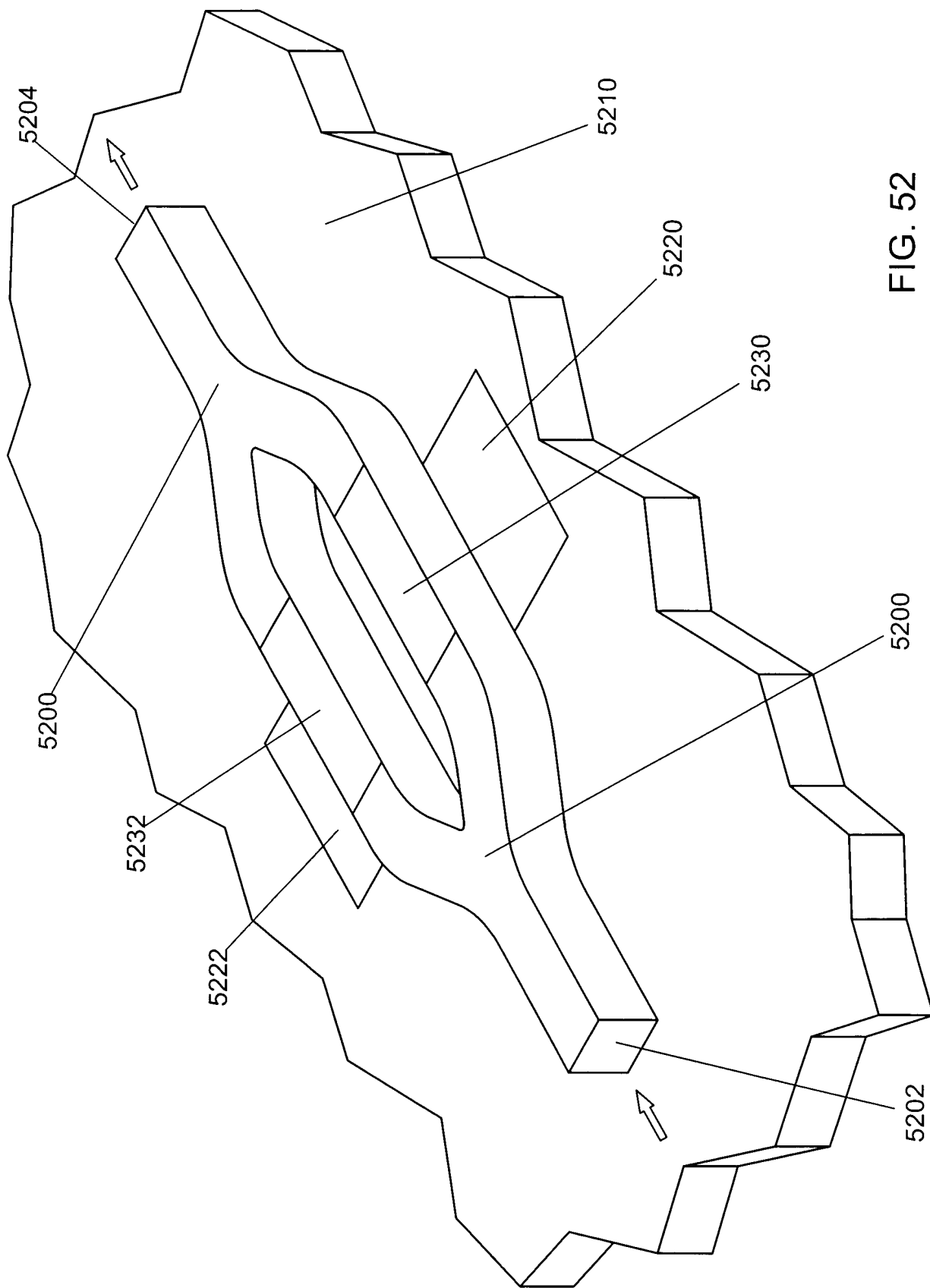
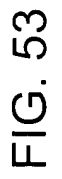


FIG. 50









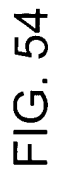


FIG. 55 is a perspective view of the device 46/53 in a folded state, showing the device 46/53 in a folded state, with the device 46/53 in a folded state, and the device 46/53 in a folded state.

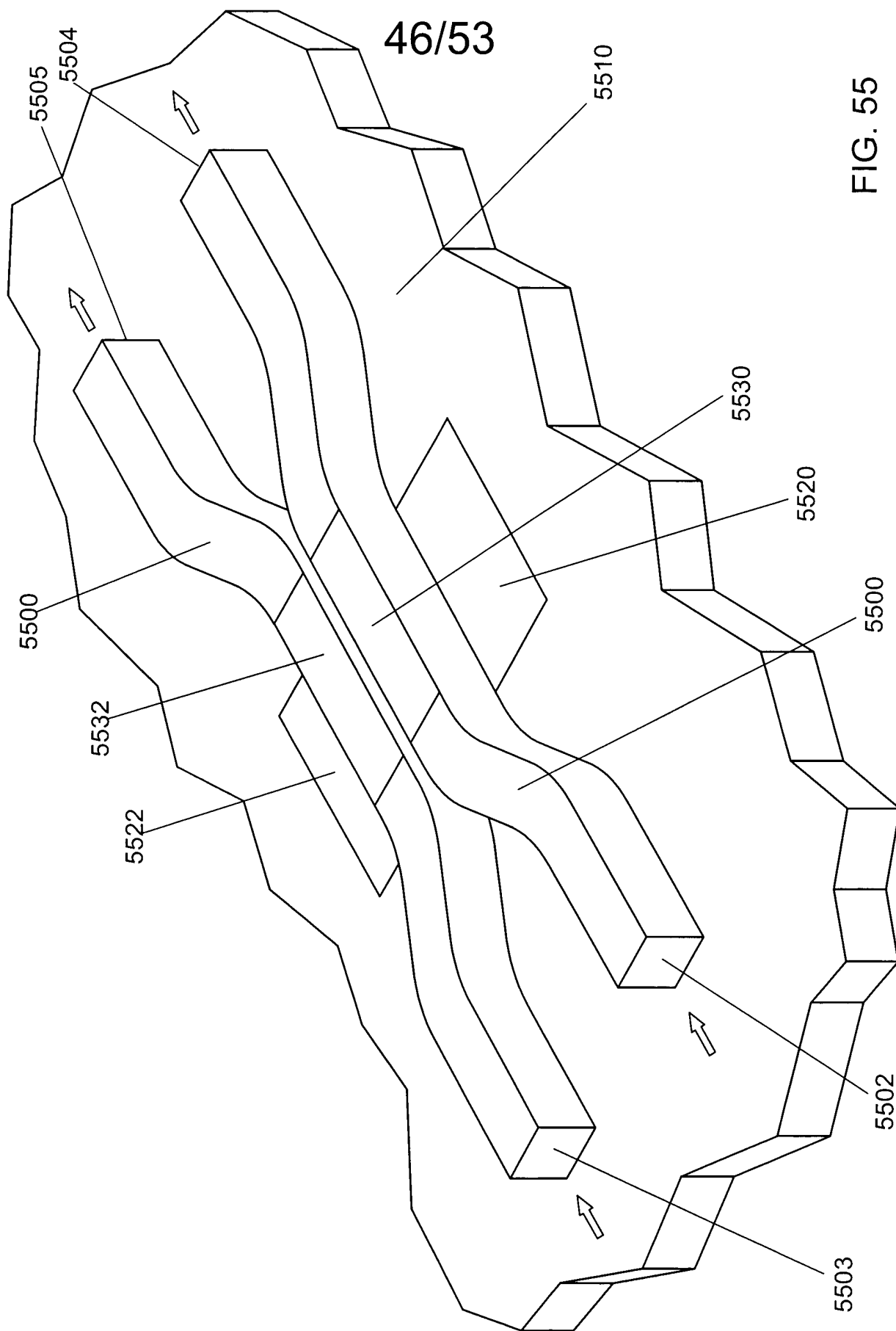


FIG. 55



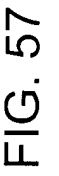
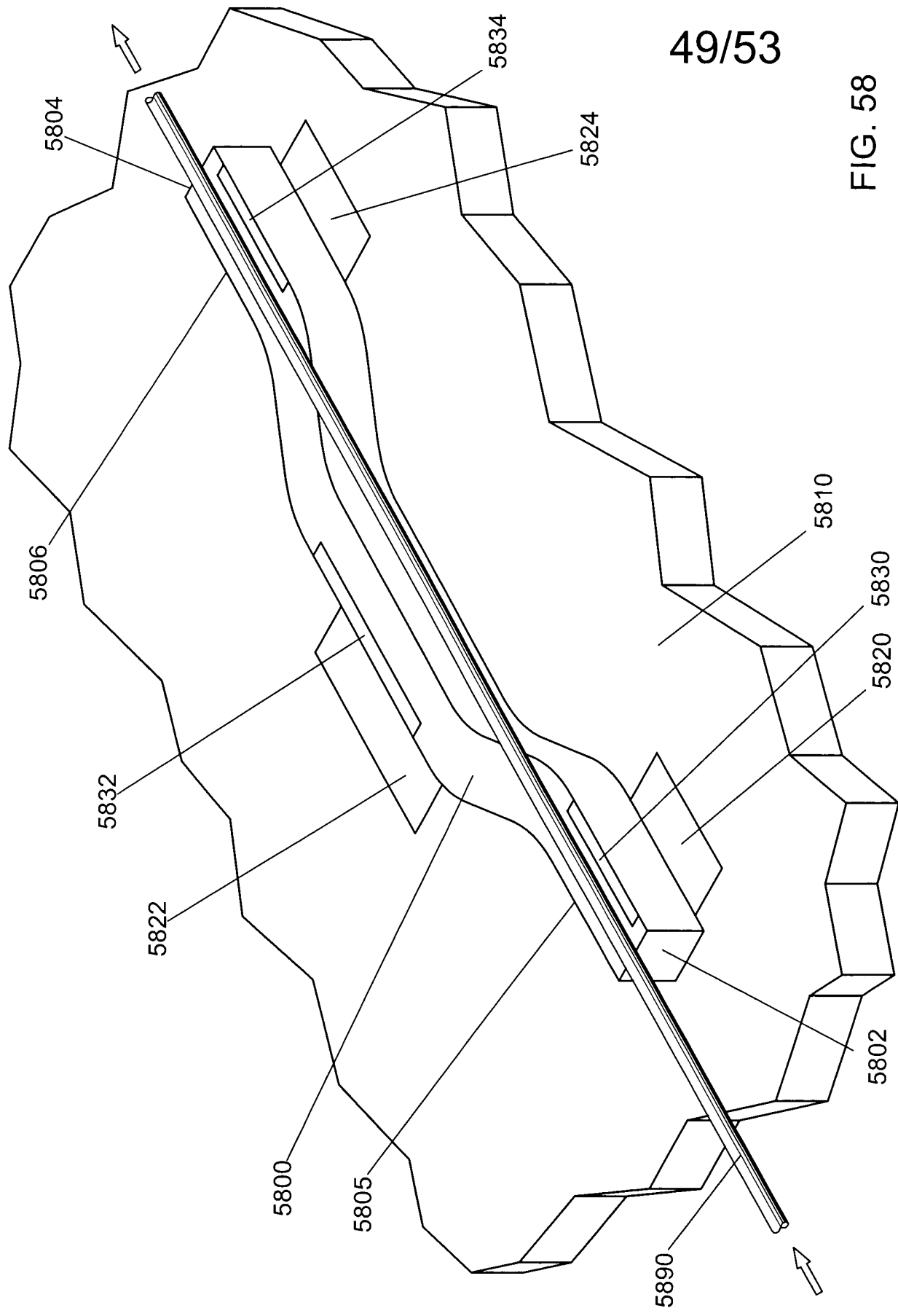




FIG. 58 is a perspective view of the device 5800 in a closed position.



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FIG. 58

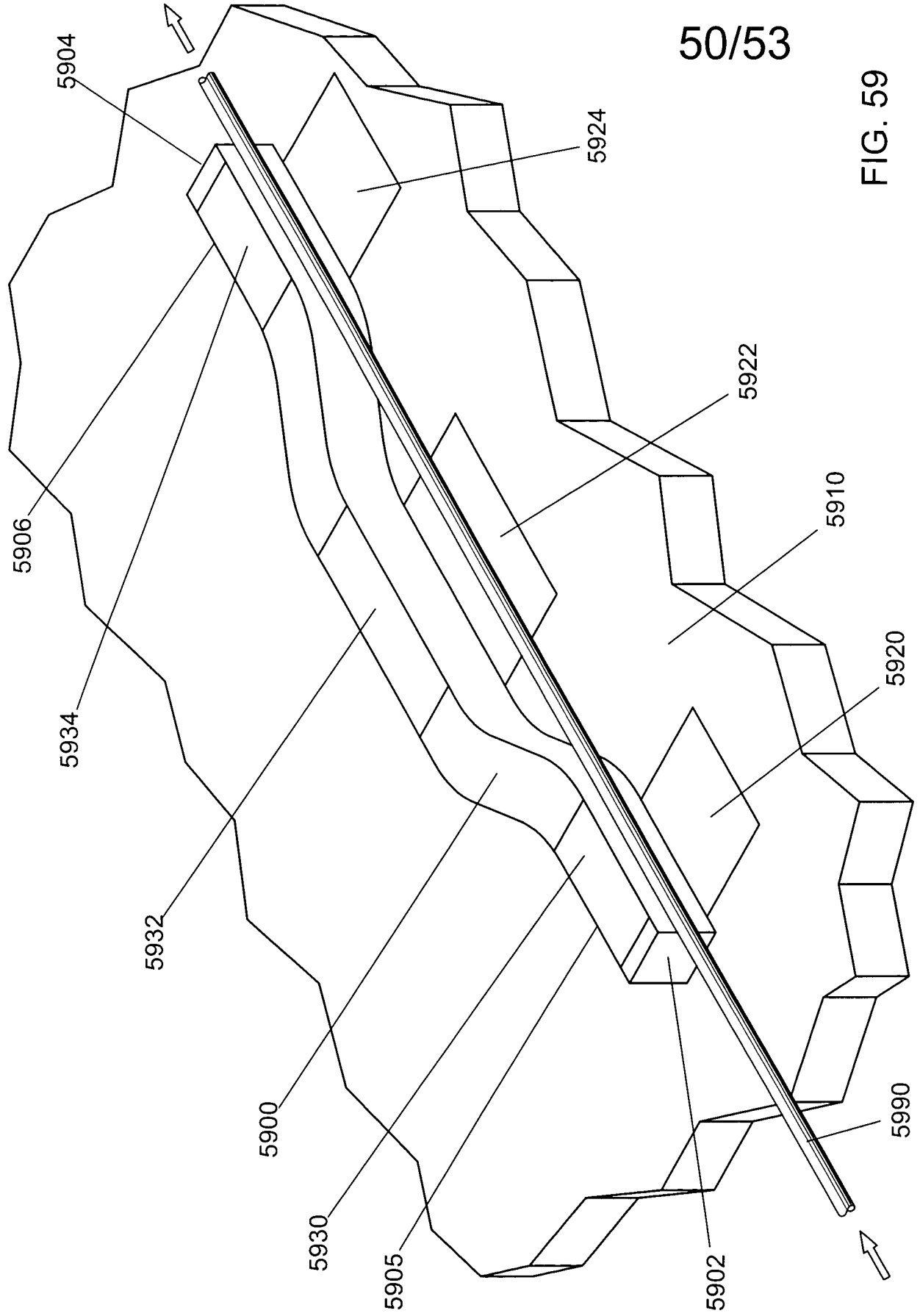
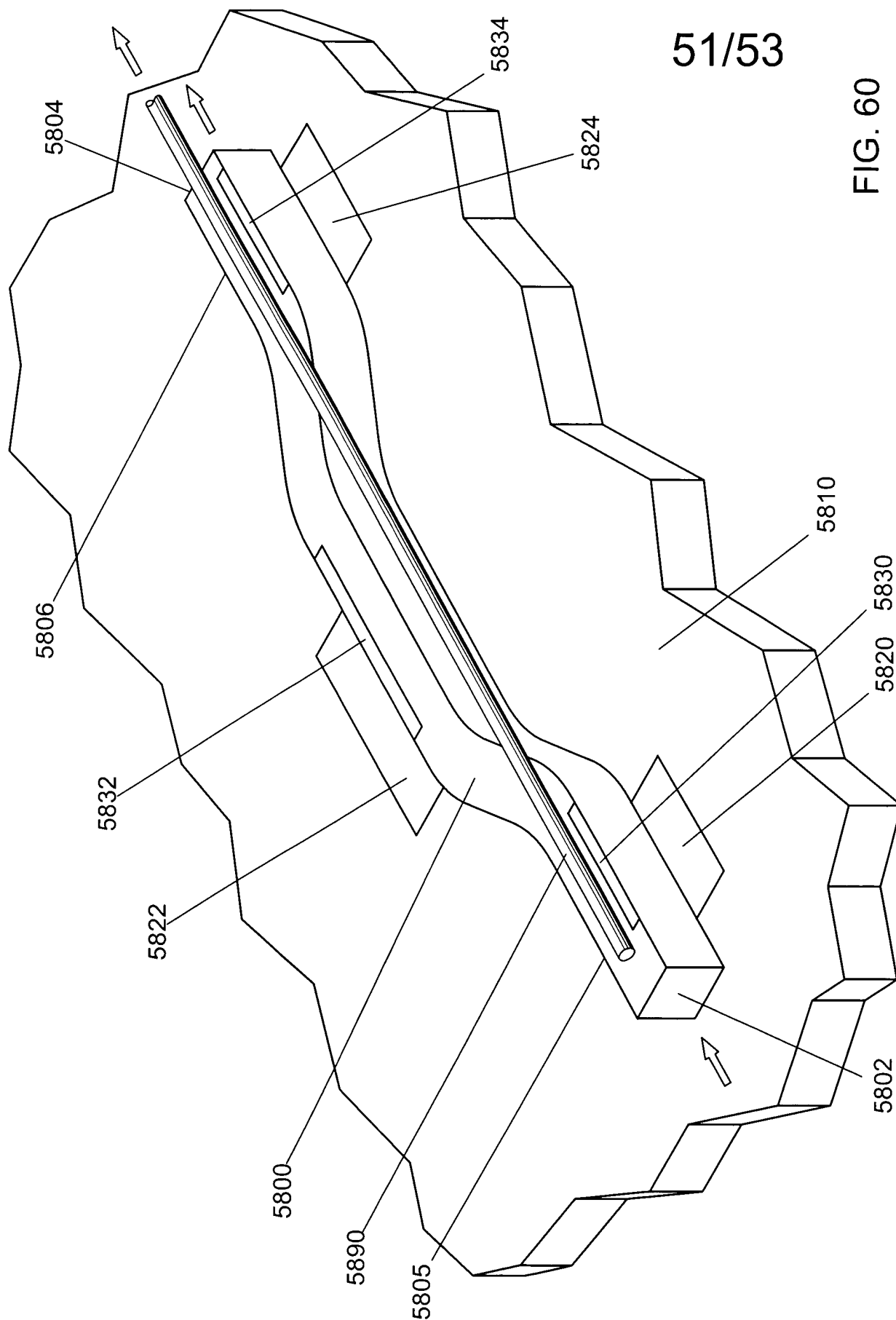


FIG. 59

FIG. 60



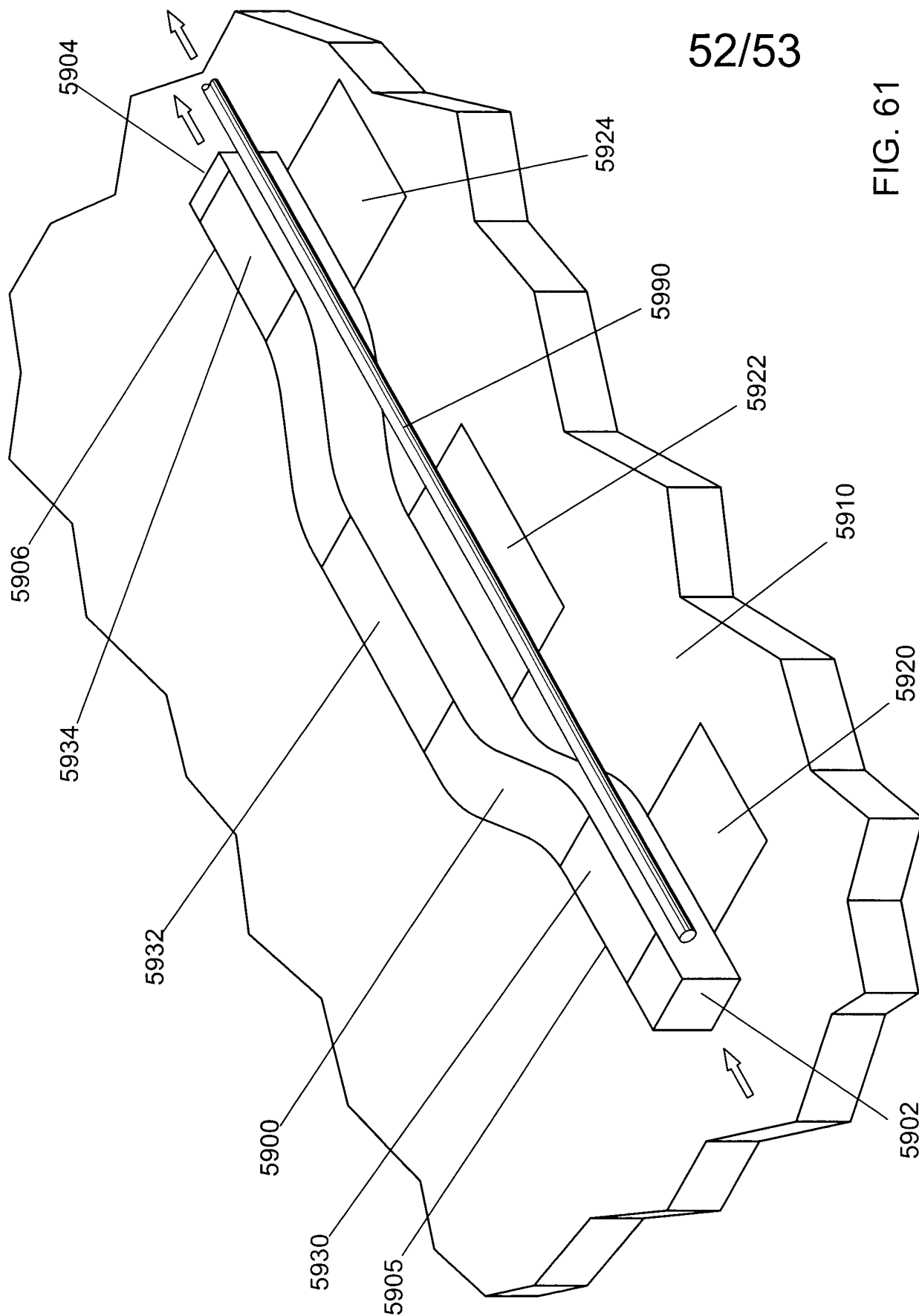


FIG. 61

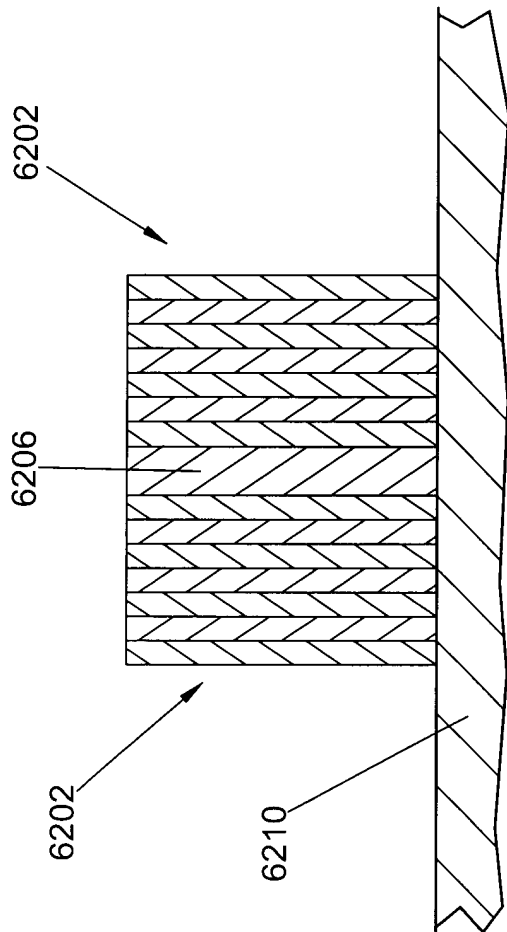


FIG. 62A

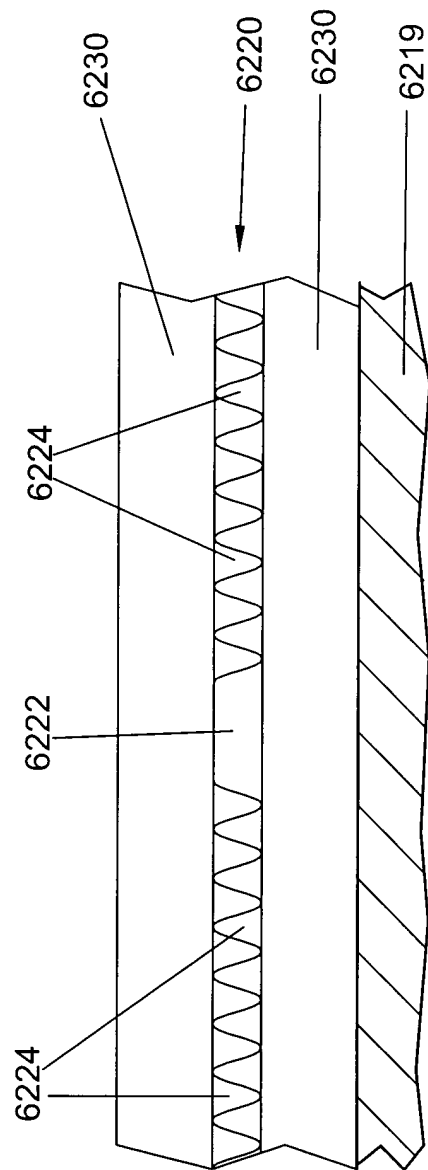


FIG. 62B